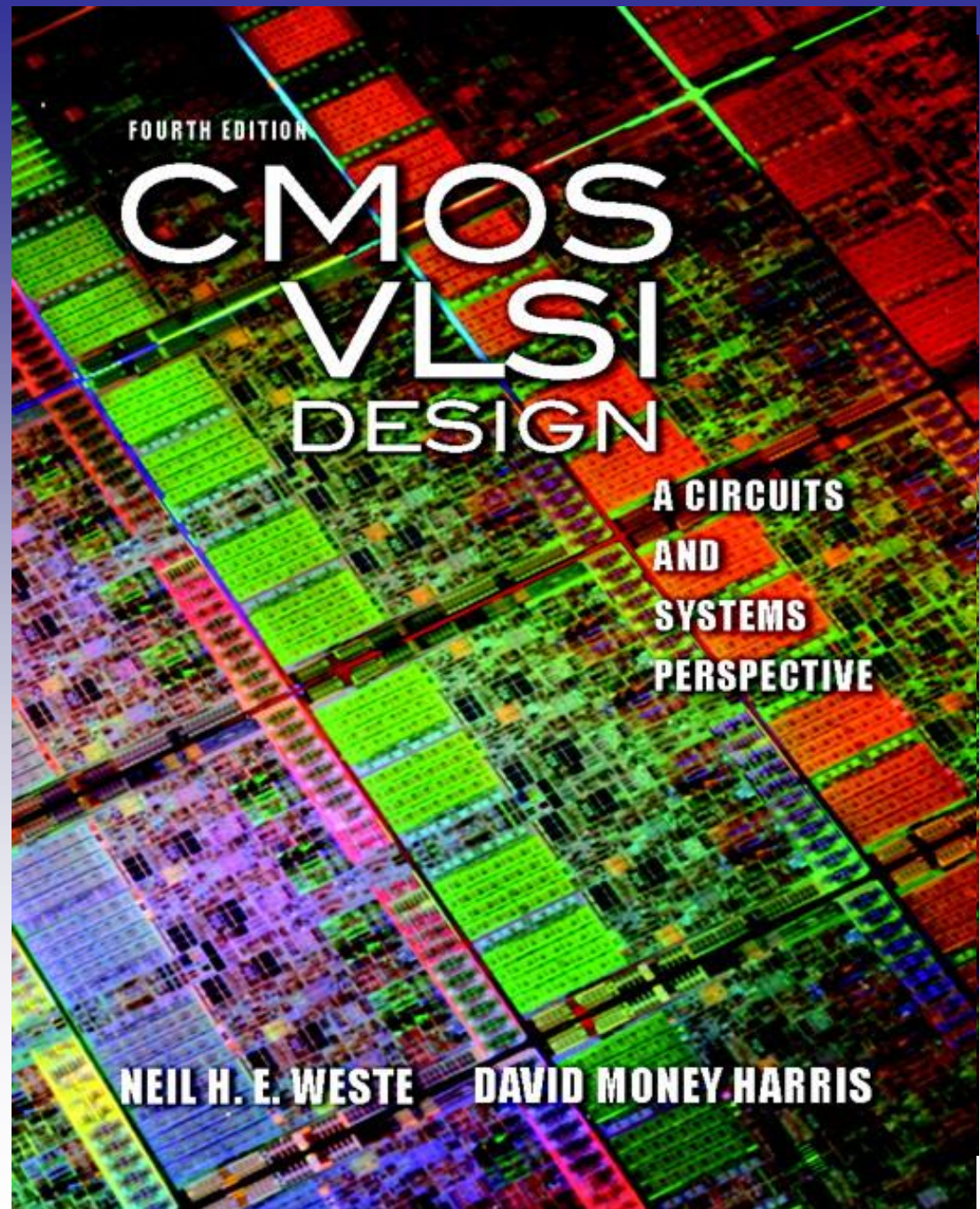


Chapter 1

Introduction

Addison-Wesley
is an imprint of

PEARSON



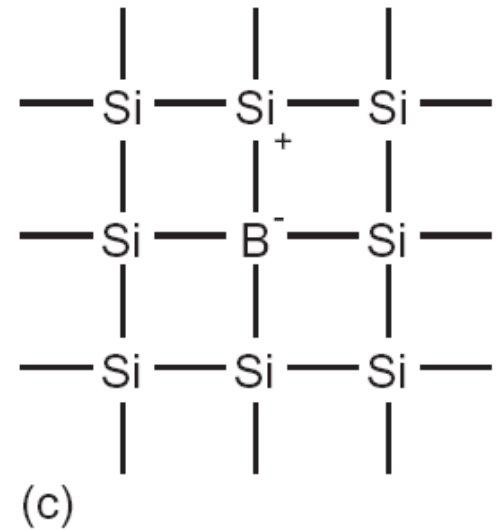
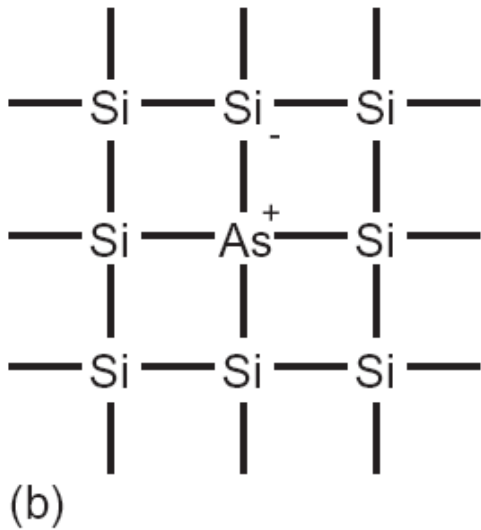
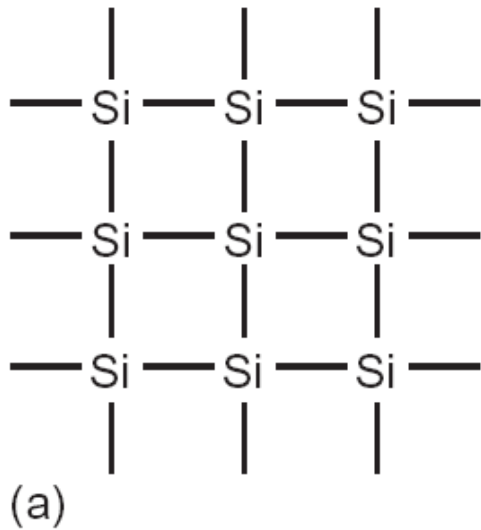


FIGURE 1.7 Silicon lattice and dopant atoms





Anode Cathode



FIGURE 1.8

p-n junction diode
structure and symbol



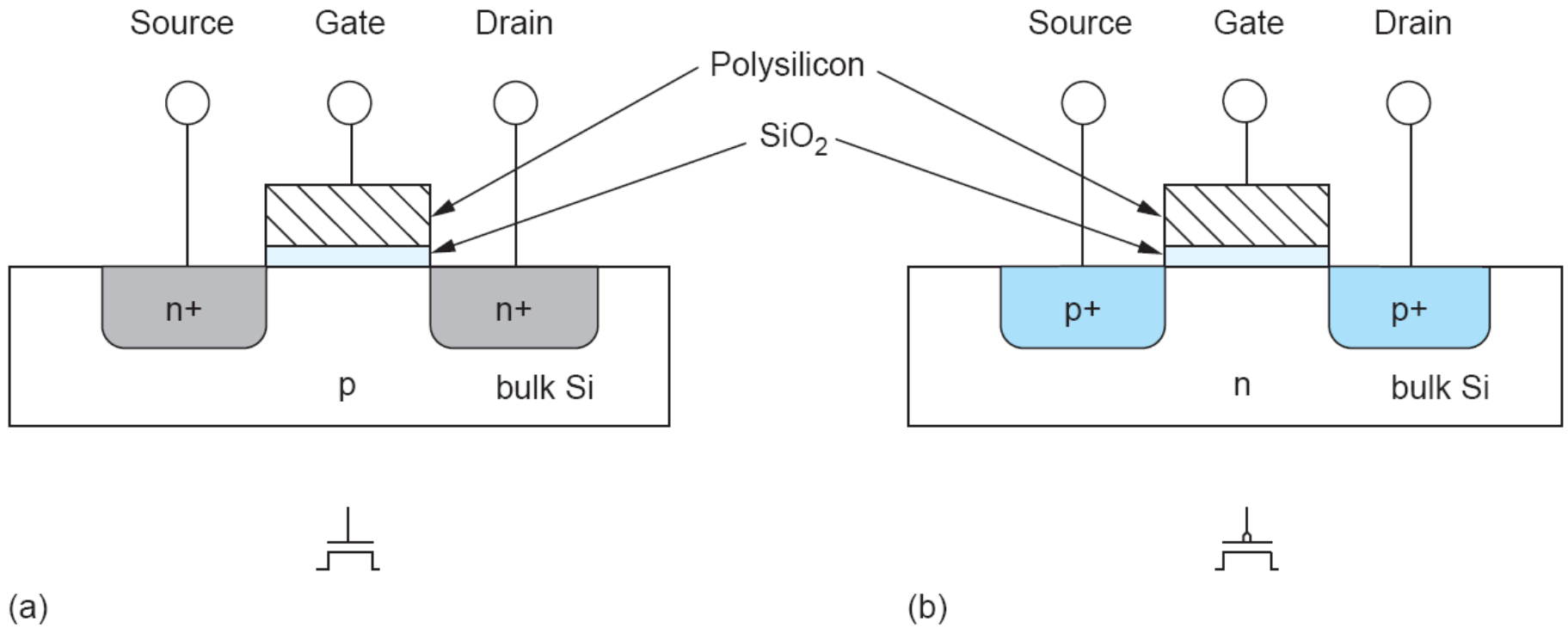
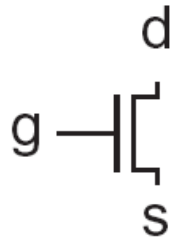


FIGURE 1.9 nMOS transistor (a) and pMOS transistor (b)

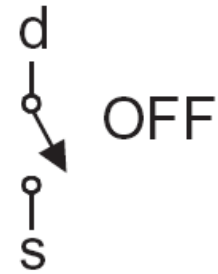




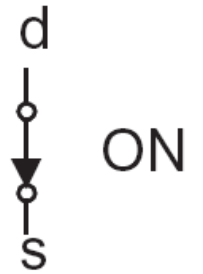
nMOS



$g = 0$



$g = 1$



pMOS

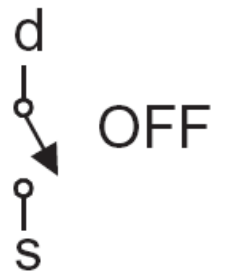
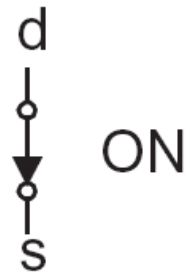
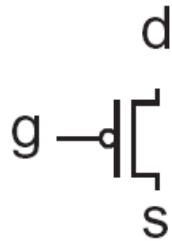
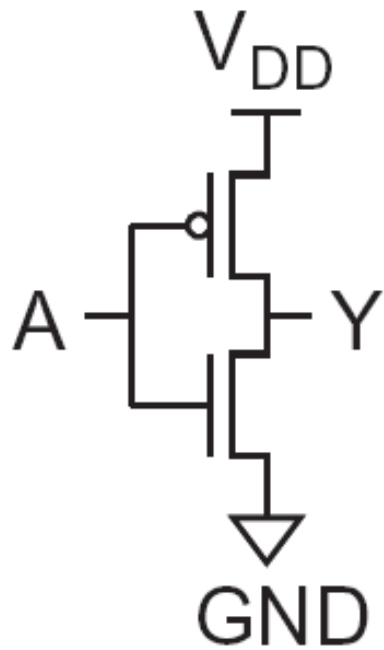
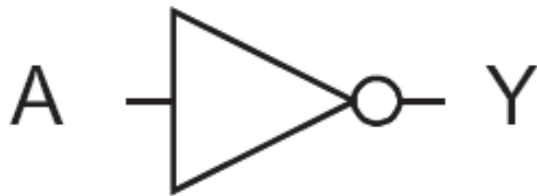


FIGURE 1.10 Transistor symbols and switch-level models





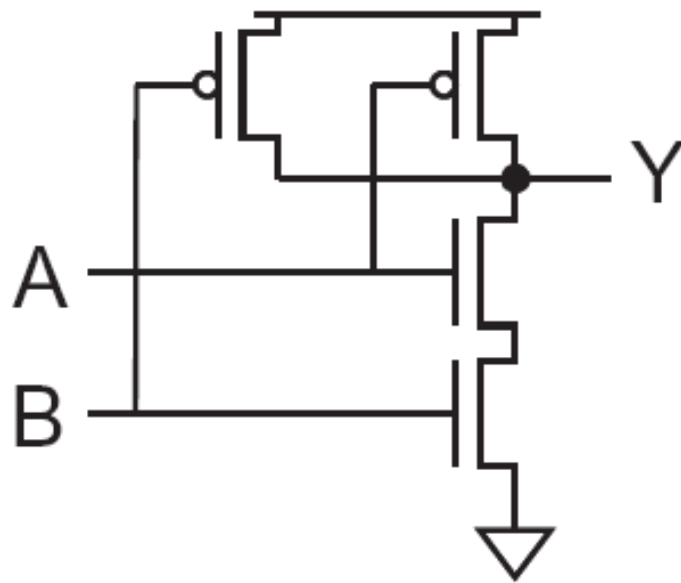
(a)



(b)

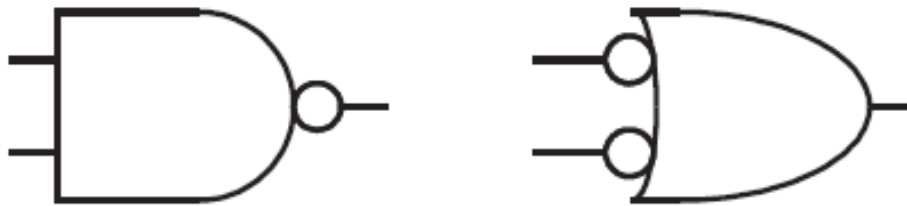
FIGURE 1.11

Inverter schematic
(a) and symbol
(b) $Y = \overline{A}$



(a)

FIGURE 1.12 2-input NAND gate schematic (a) and symbol (b) $Y = \overline{A \cdot B}$



(b)

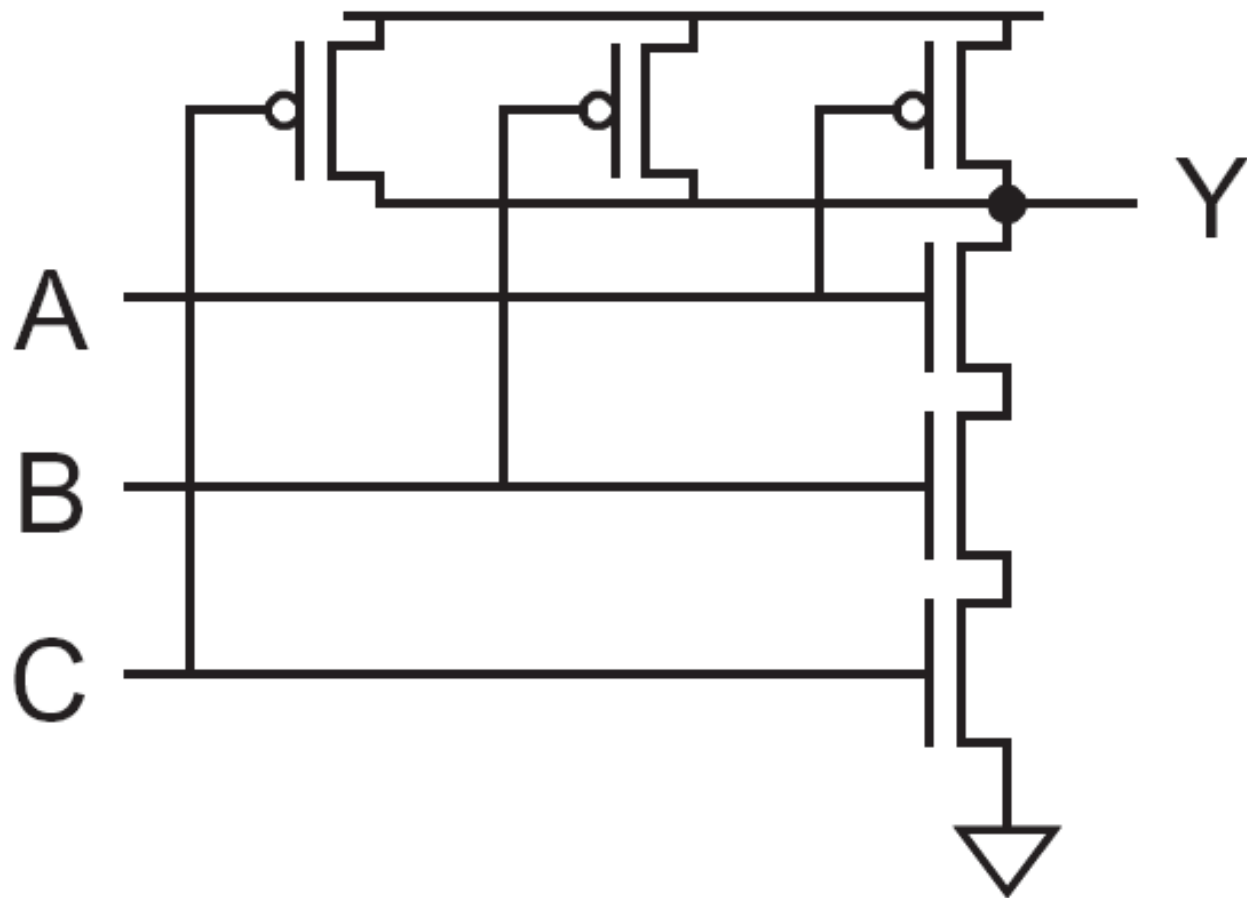


FIGURE 1.13 3-input NAND
gate schematic $Y = \overline{A \cdot B \cdot C}$

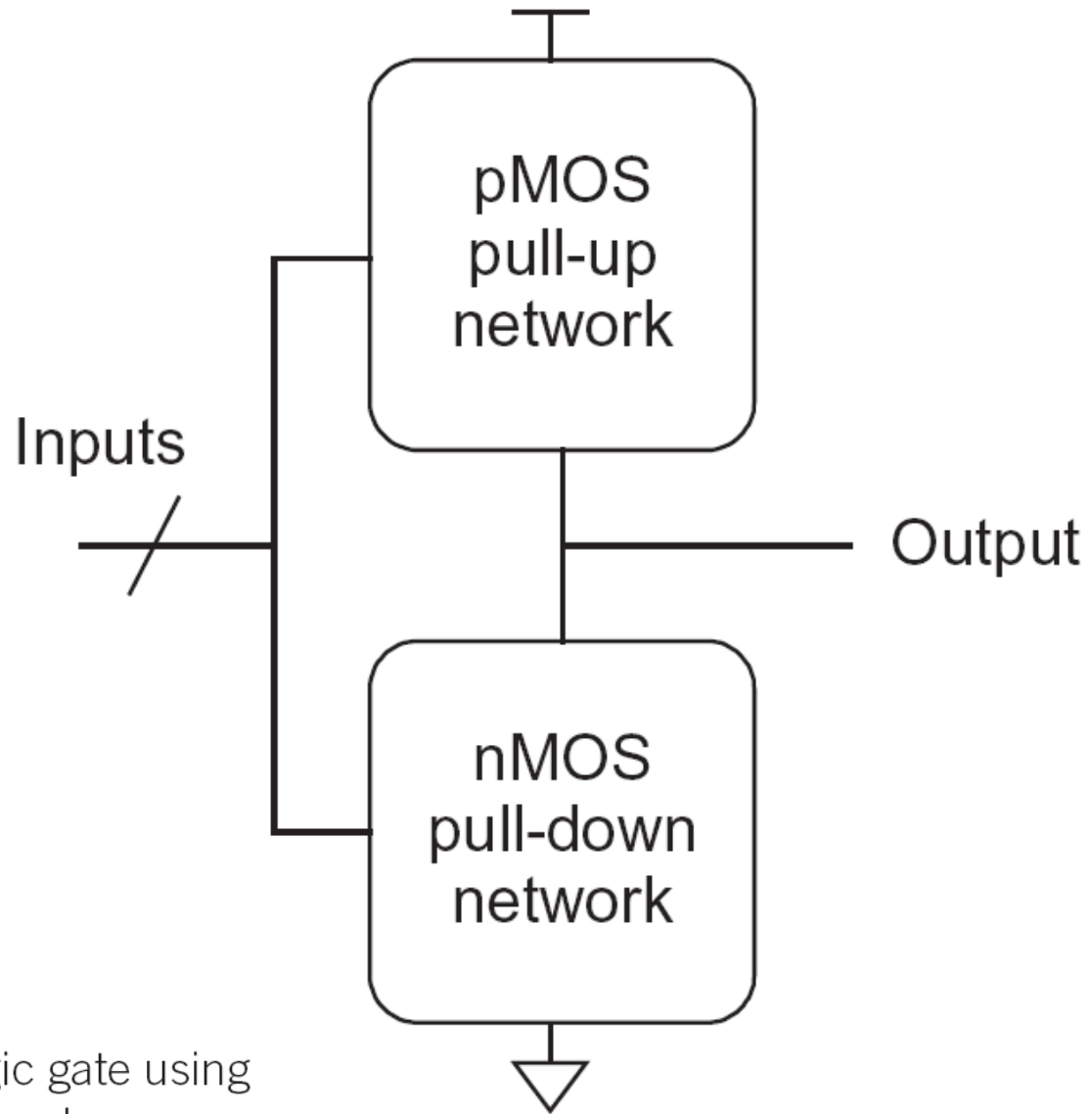
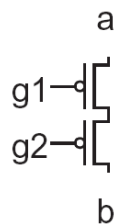
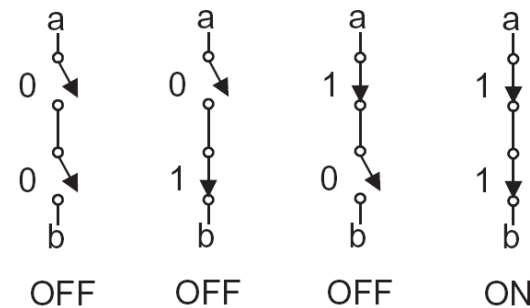


FIGURE 1.14 General logic gate using pull-up and pull-down networks

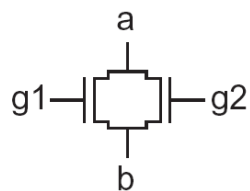
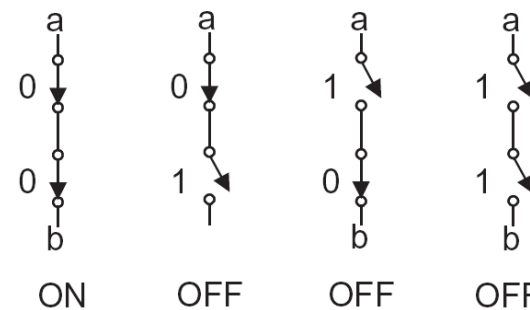




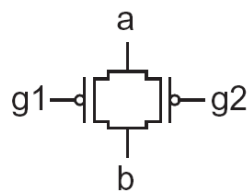
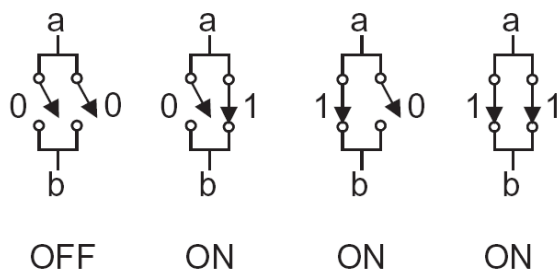
(a)



(b)



(c)



(d)

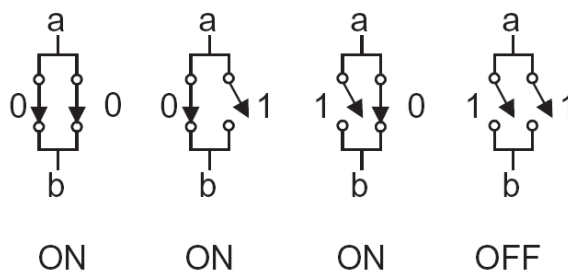
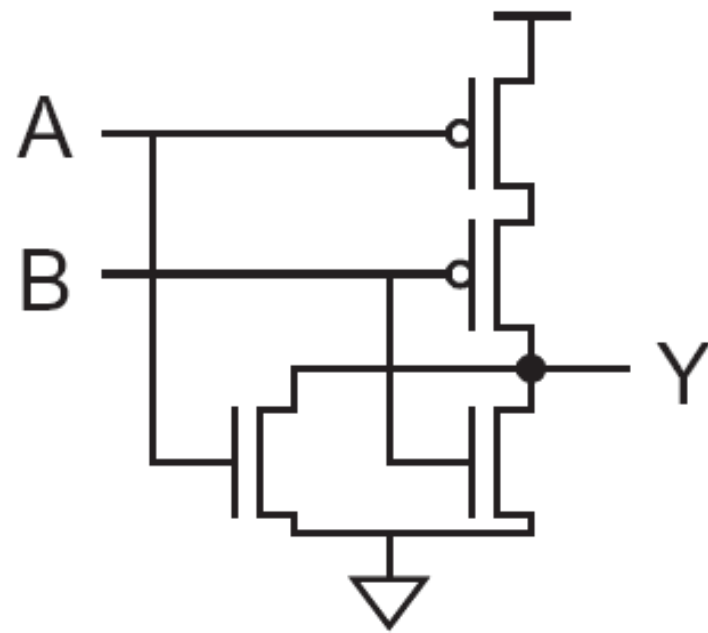
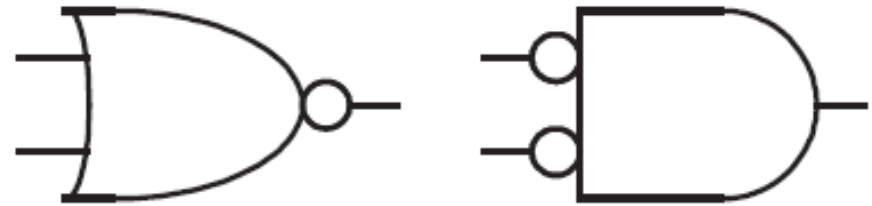


FIGURE 1.15

Connection and behavior of series and parallel transistors



(a)



(b)

FIGURE 1.16 2-input NOR gate schematic (a) and symbol (b) $Y = \overline{A + B}$



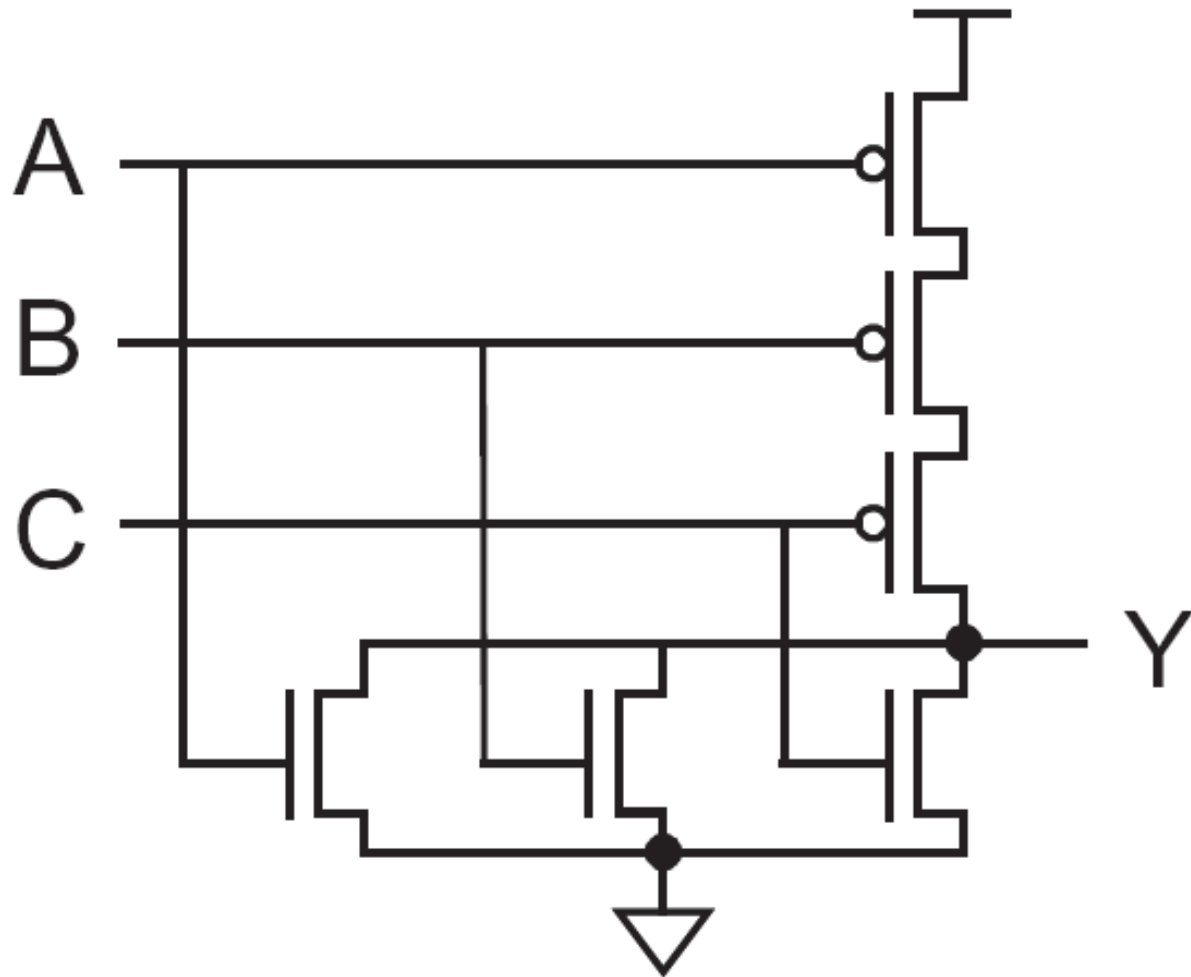
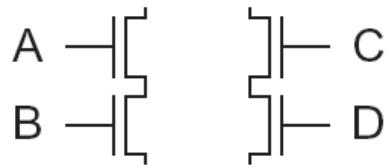
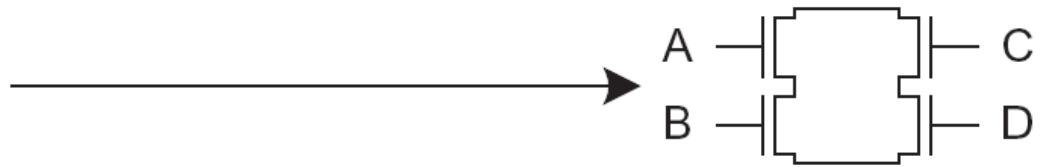


FIGURE 1.17 3-input NOR
gate schematic $Y = \overline{A + B + C}$



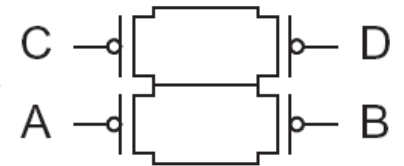
(a)



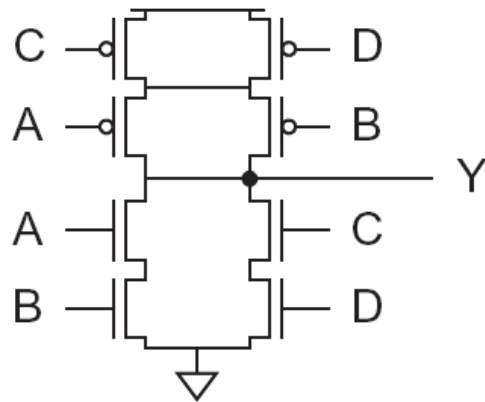
(b)



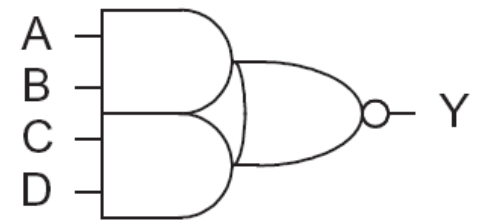
(c)



(d)



(e)



(f)

FIGURE 1.18 CMOS compound gate for function $Y = \overline{(A \cdot B) + (C \cdot D)}$



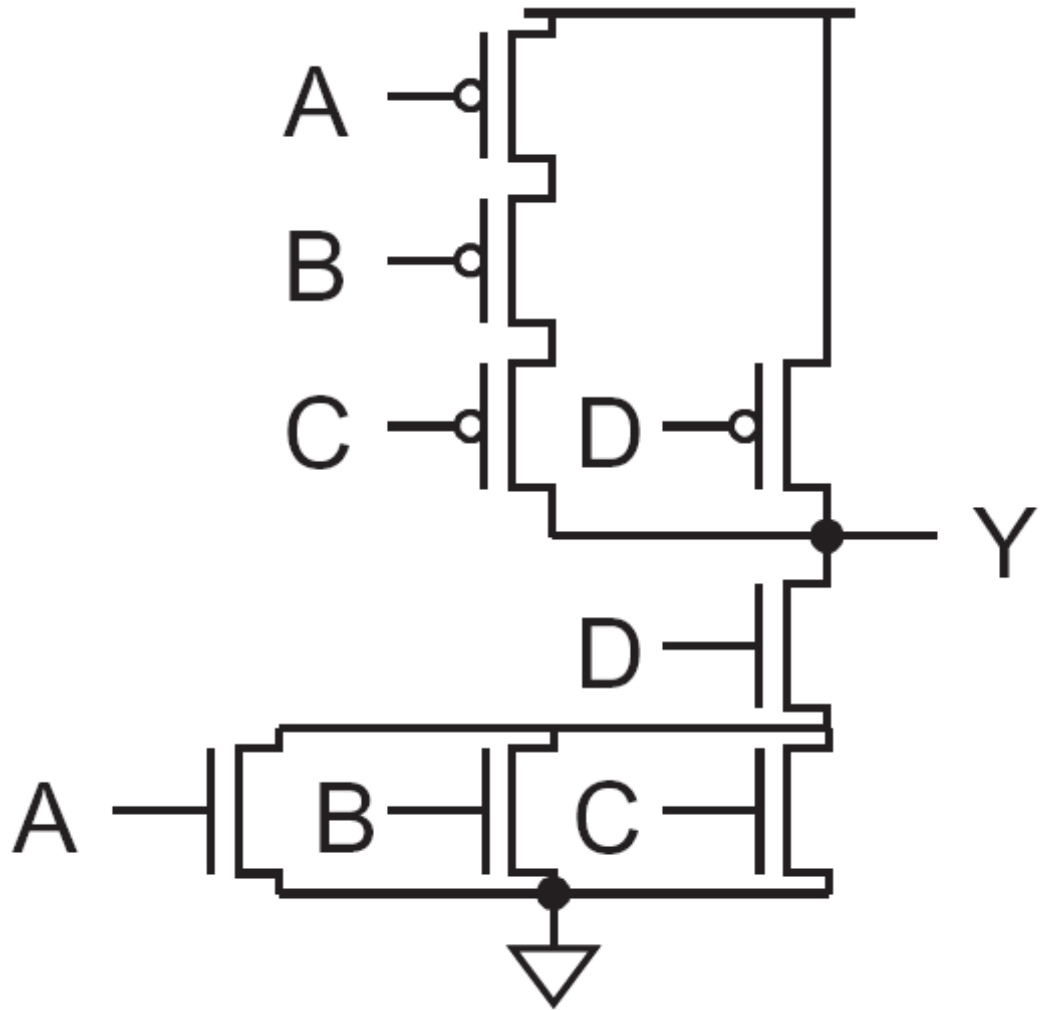


FIGURE 1.19

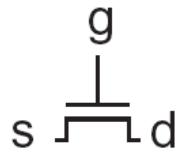
CMOS compound gate
for function

$$Y = \overline{(A + B + C)} \cdot D$$

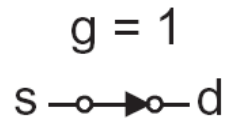
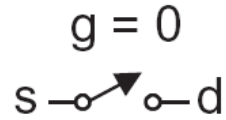




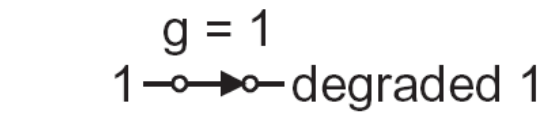
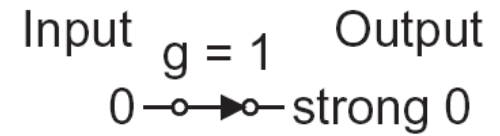
nMOS



(a)

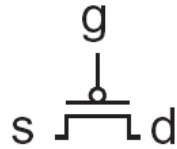


(b)

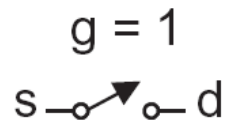
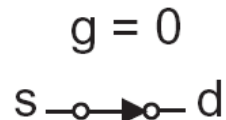


(c)

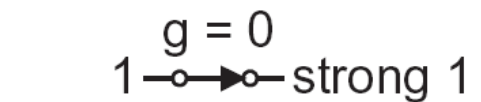
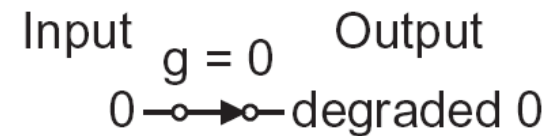
pMOS



(d)



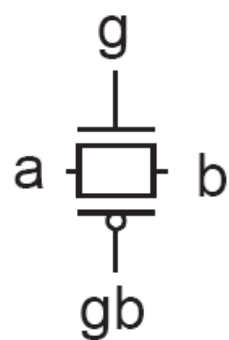
(e)



(f)

FIGURE 1.20 Pass transistor strong and degraded outputs





(a)

$$g = 0, gb = 1$$



$$g = 1, gb = 0$$

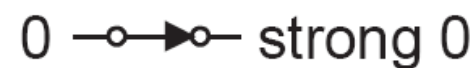


(b)

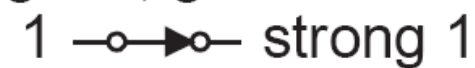
Input

Output

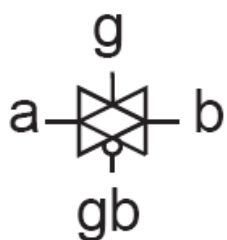
$$g = 1, gb = 0$$



$$g = 1, gb = 0$$



(c)



(d)

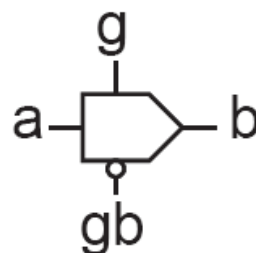
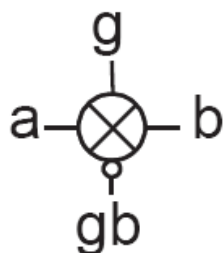


FIGURE 1.21 Transmission gate





BAD

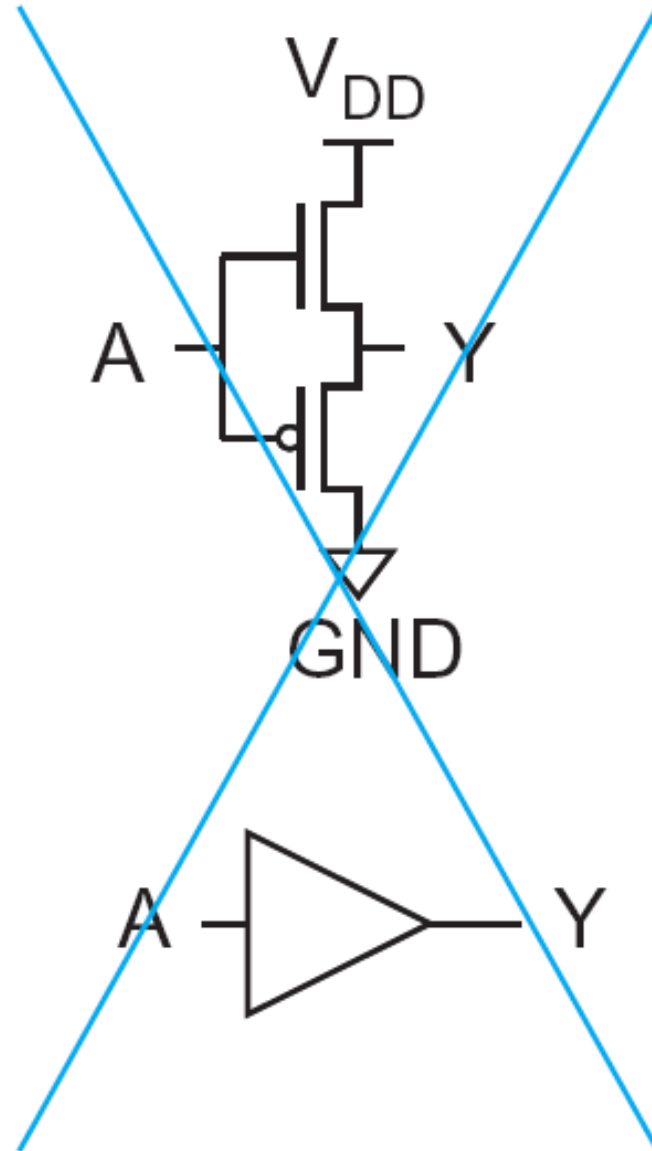


FIGURE 1.22

Bad noninverting buffer

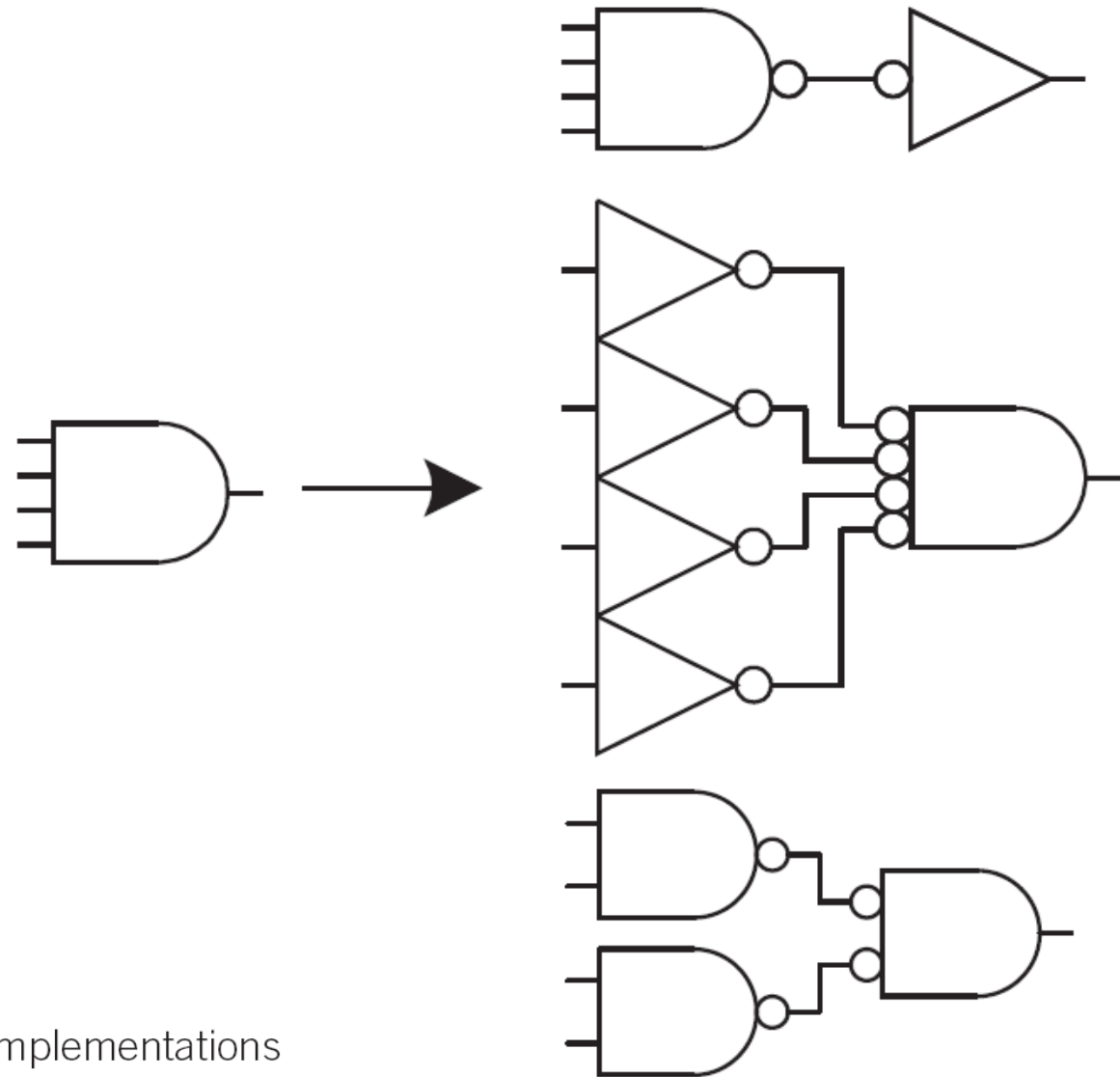


FIGURE 1.23 Various implementations of a CMOS 4-input AND gate



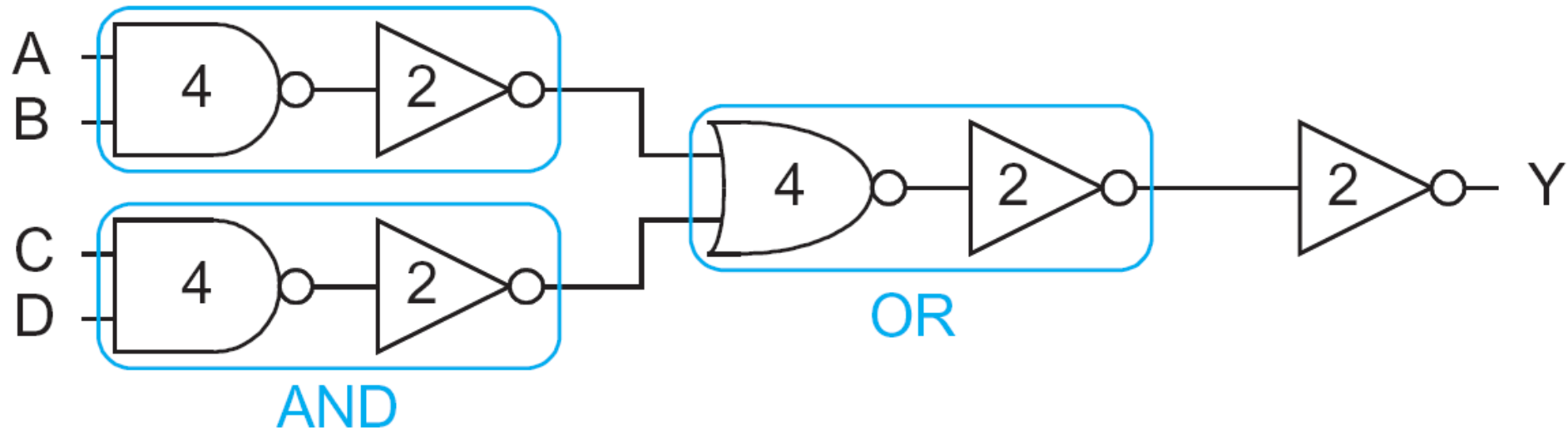


FIGURE 1.24 Inefficient discrete gate implementation of AOI22 with transistor counts indicated



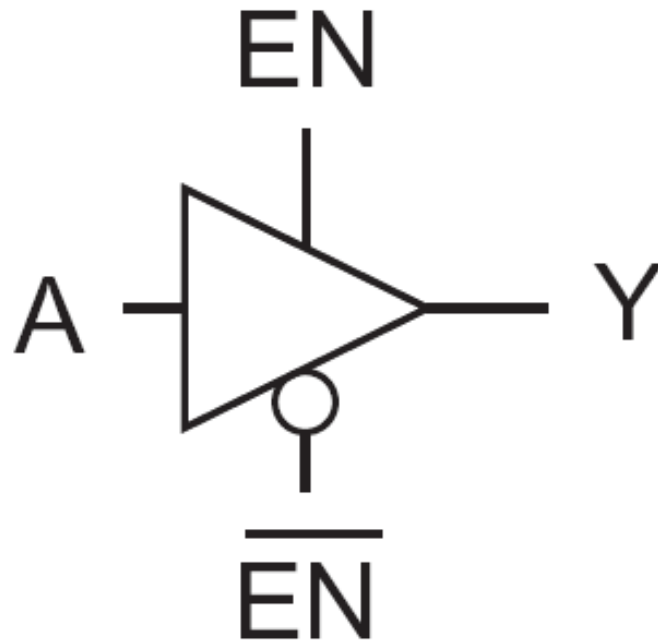
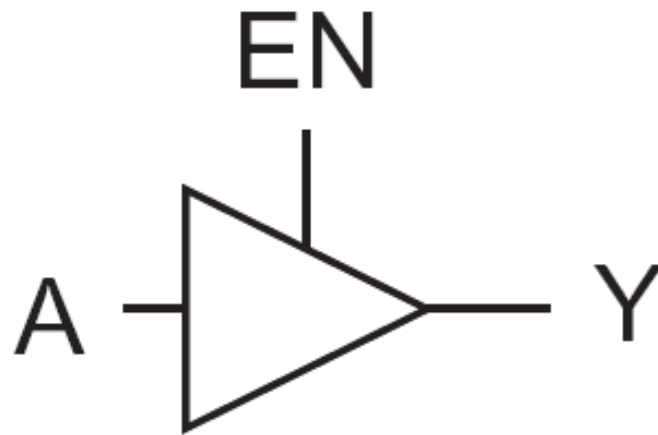


FIGURE 1.25
Tristate buffer
symbol

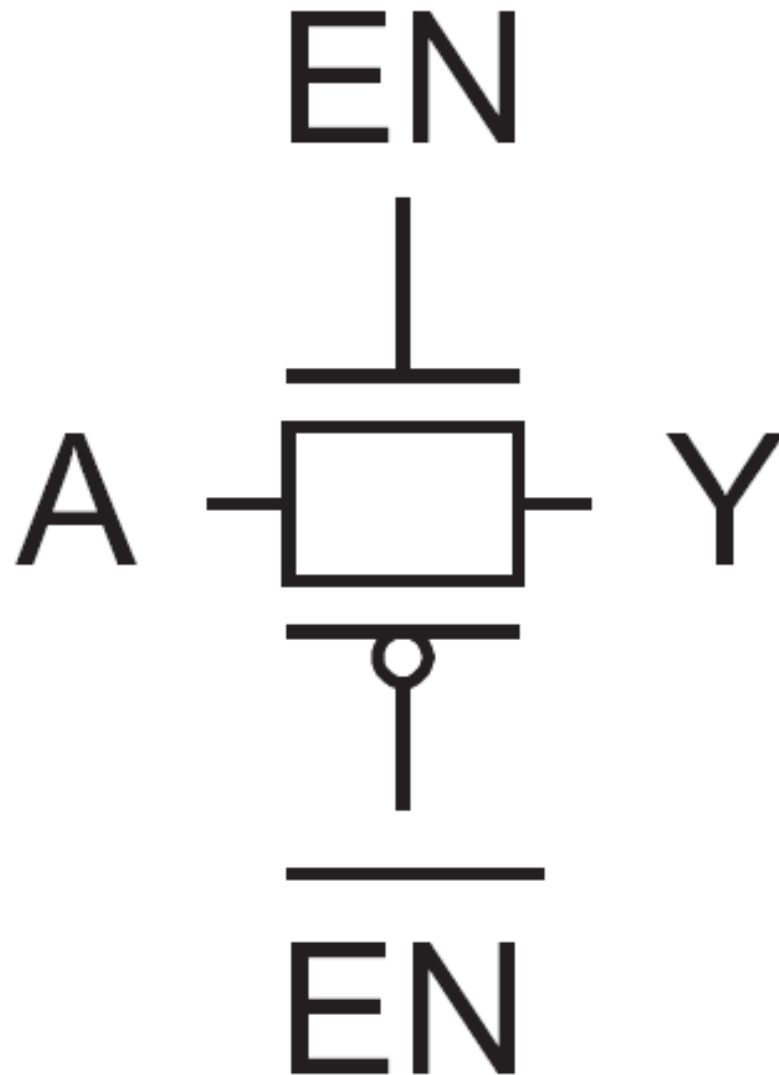


FIGURE 1.26

Transmission gate

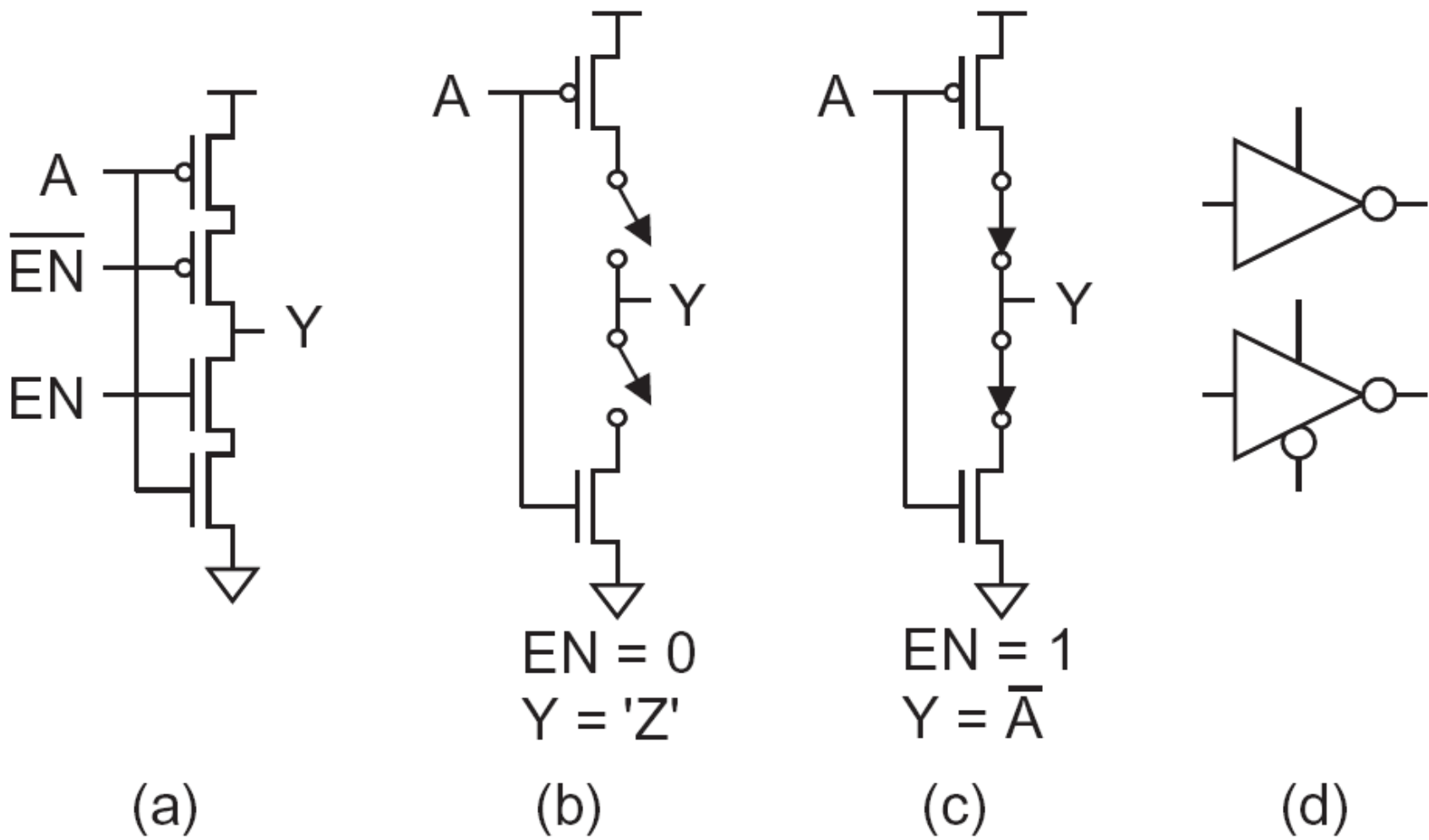
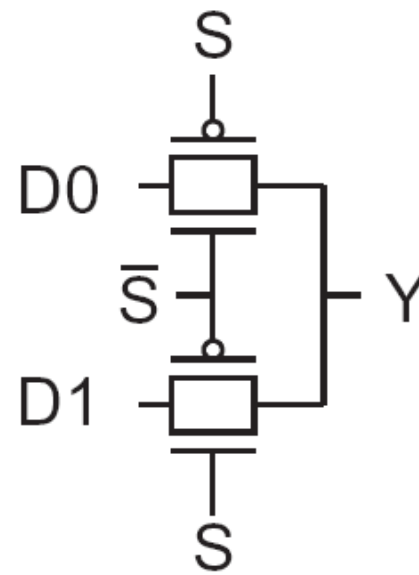
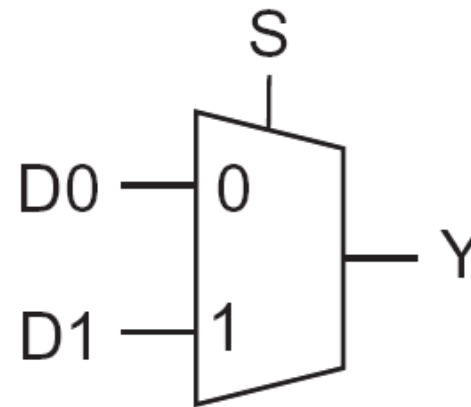


FIGURE 1.27 Tristate Inverter





(a)



(b)

FIGURE 1.28 Transmission gate multiplexer



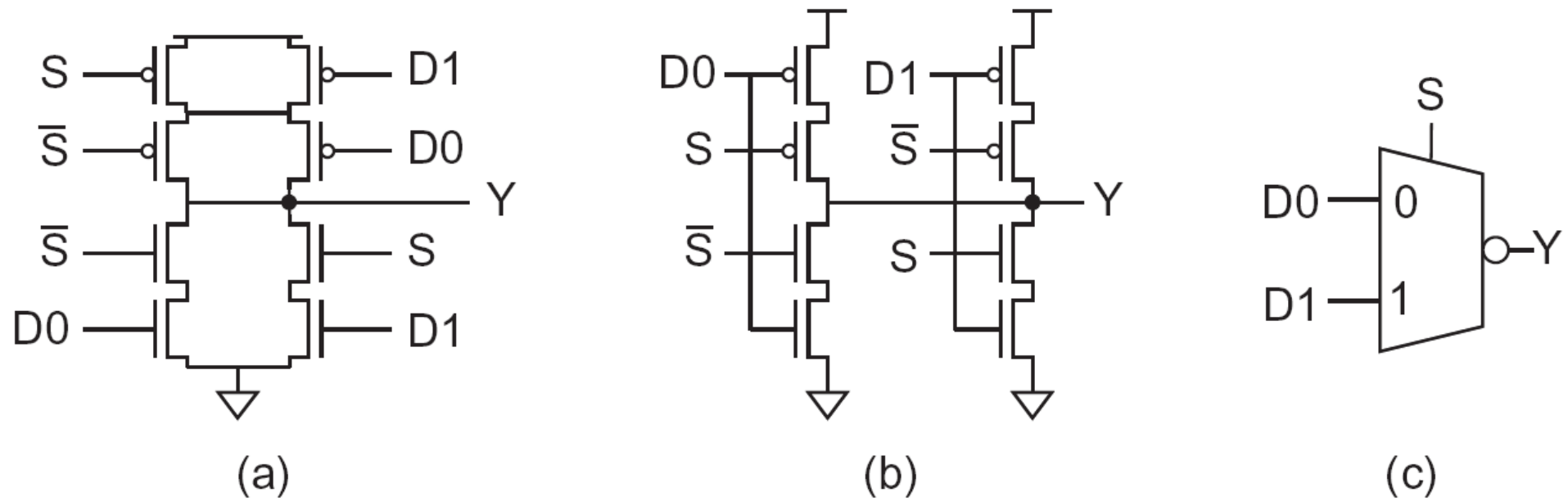
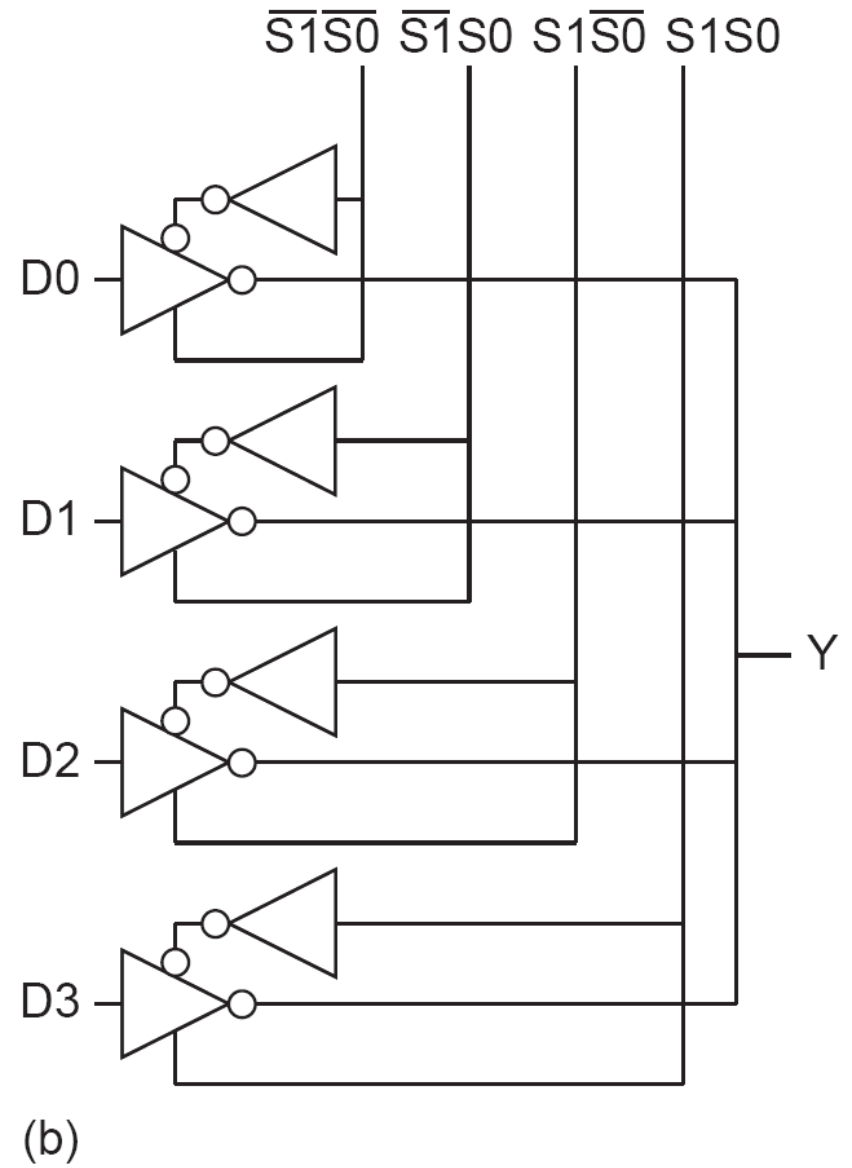
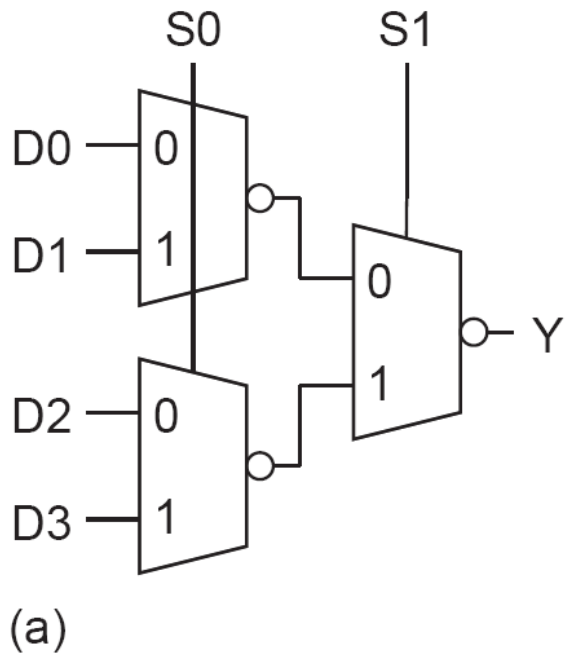


FIGURE 1.29 Inverting multiplexer





FIGURE 1.30 4:1 multiplexer



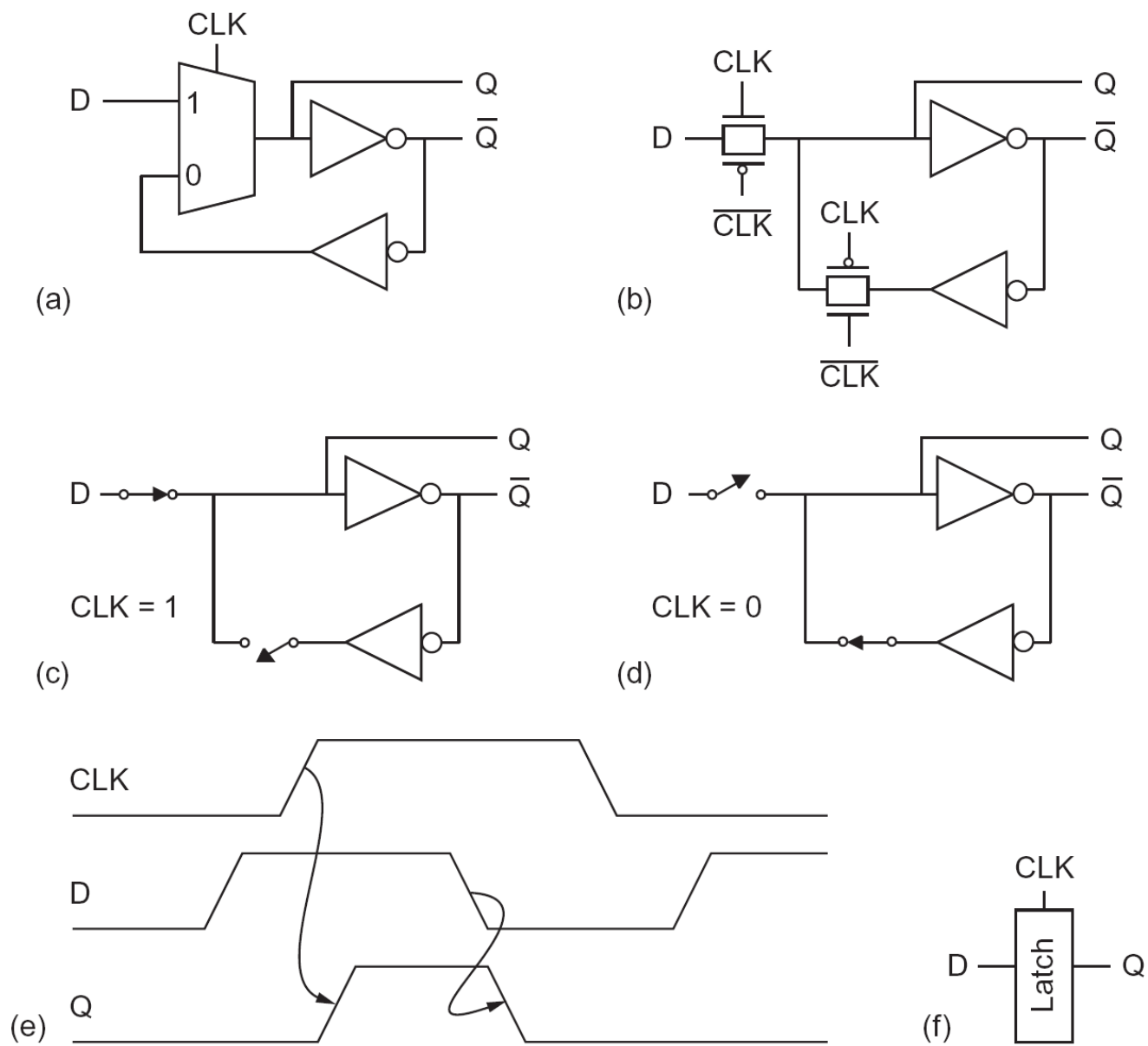
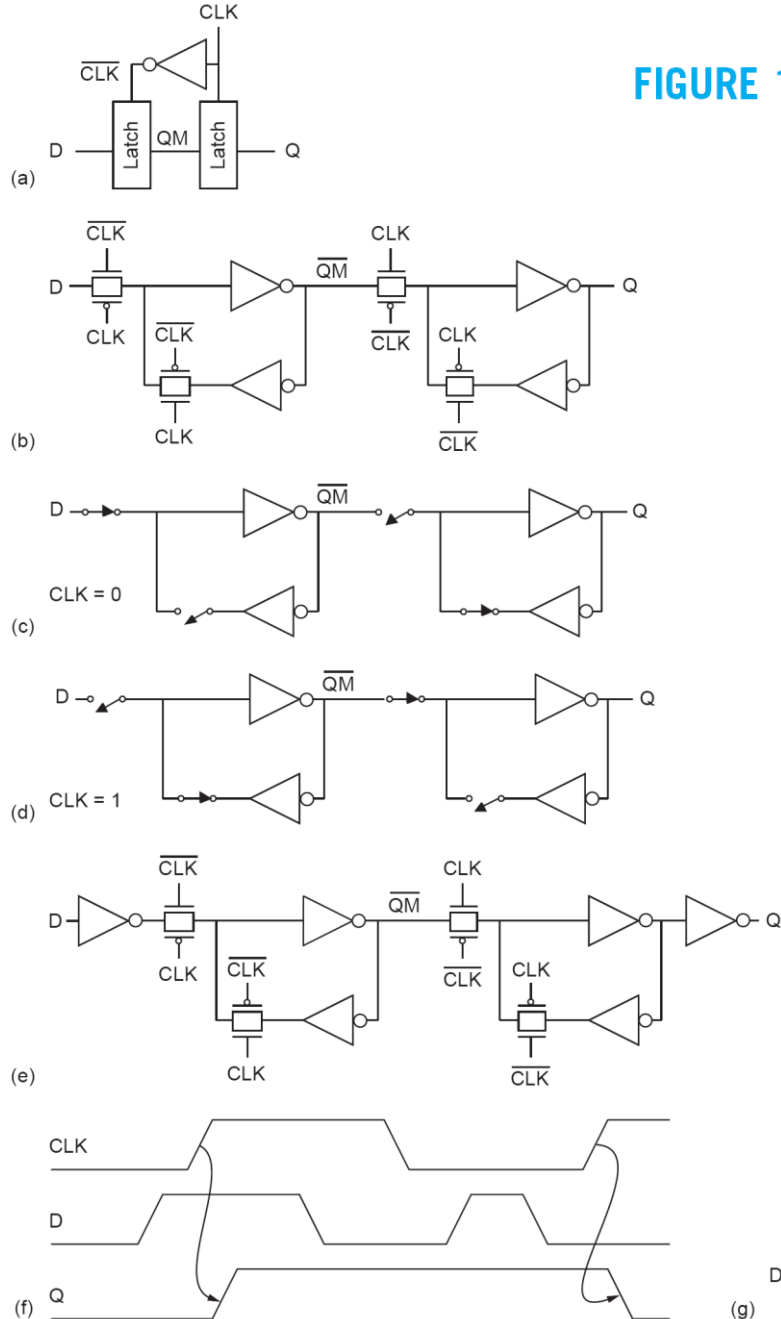


FIGURE 1.31 CMOS positive-level-sensitive D latch





FIGURE 1.32 CMOS positive-edge-triggered *D* flip-flop





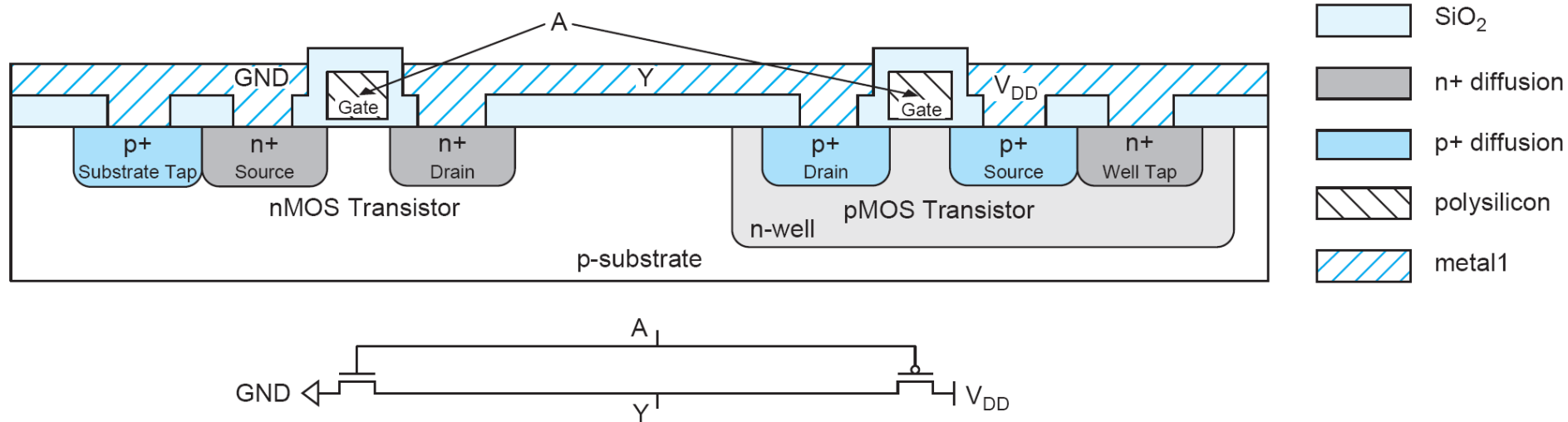


FIGURE 1.34 Inverter cross-section with well and substrate contacts. Color version on inside front cover.

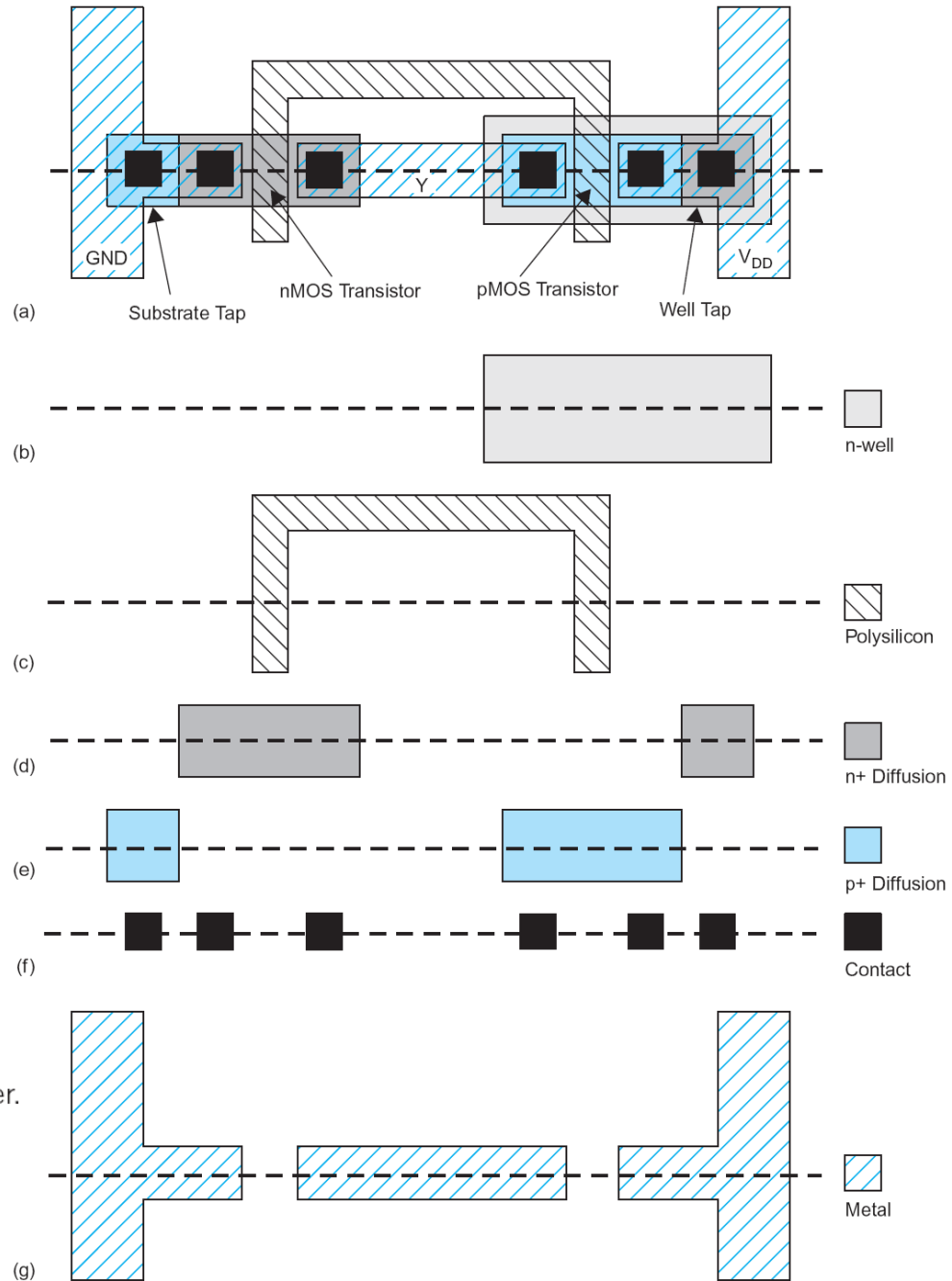


FIGURE 1.35 Inverter mask set. Color version on inside front cover.



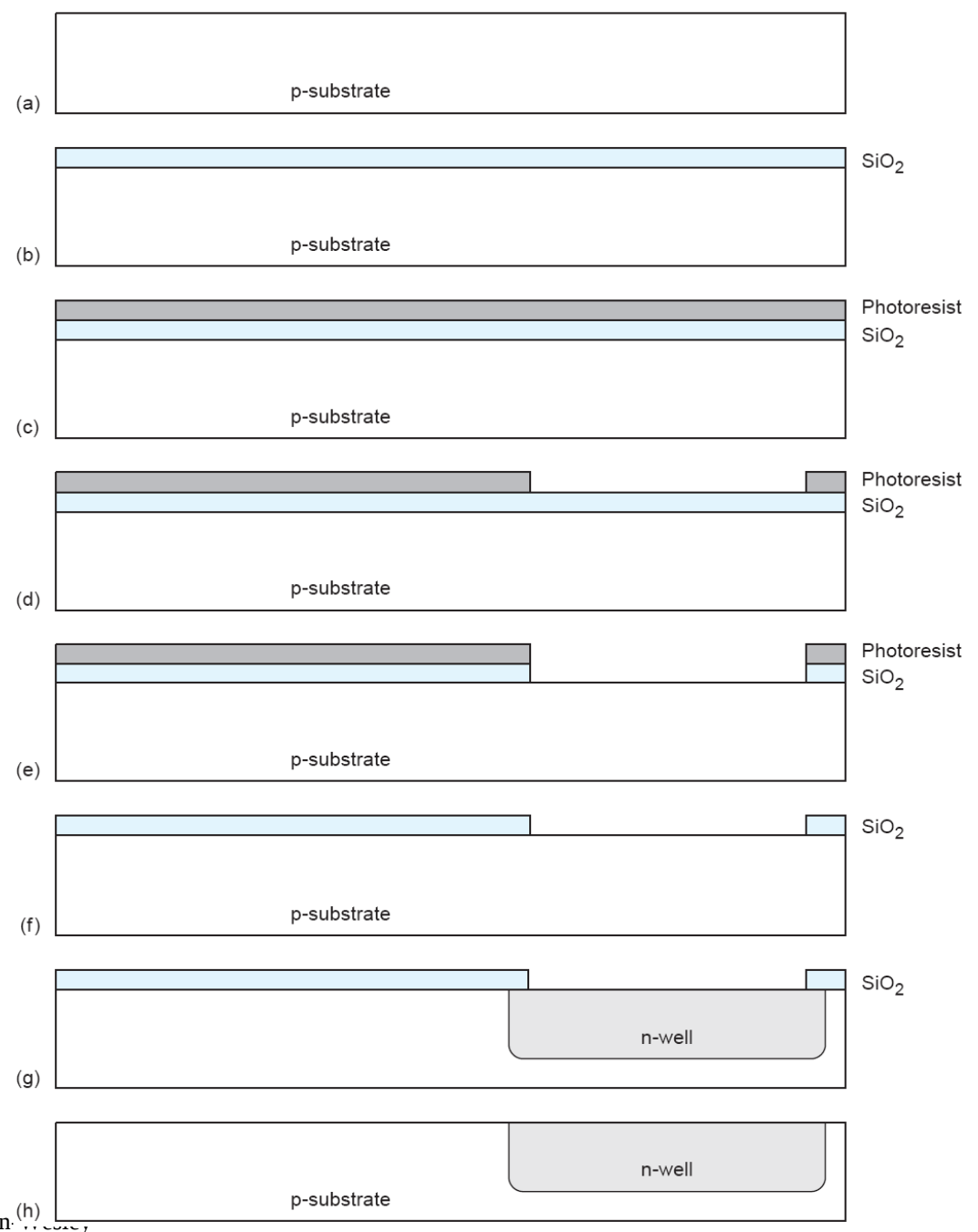


FIGURE 1.36 Cross-sections while manufacturing the n-well



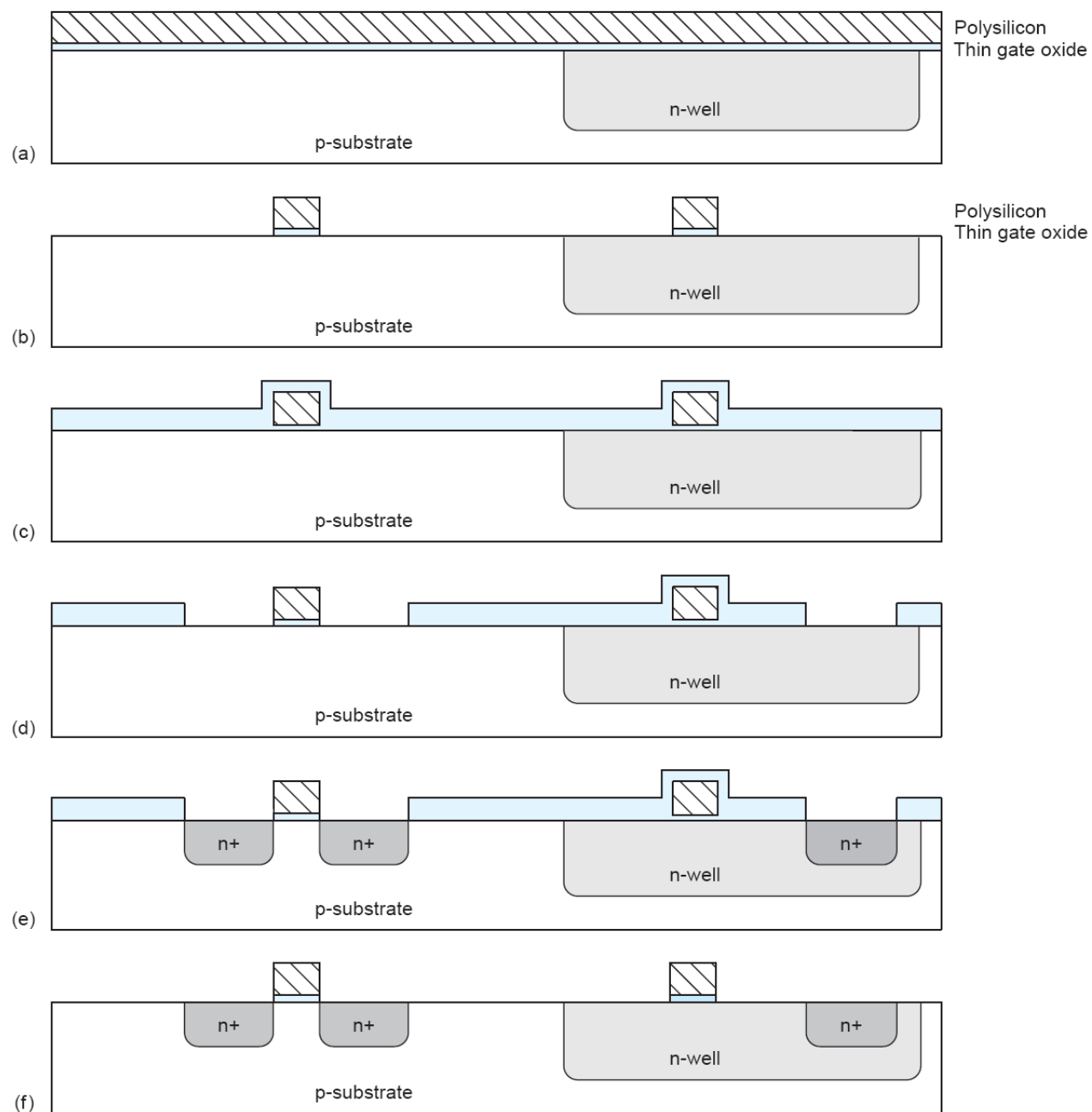


FIGURE 1.37
Cross-sections while manufacturing
polysilicon and n-diffusion



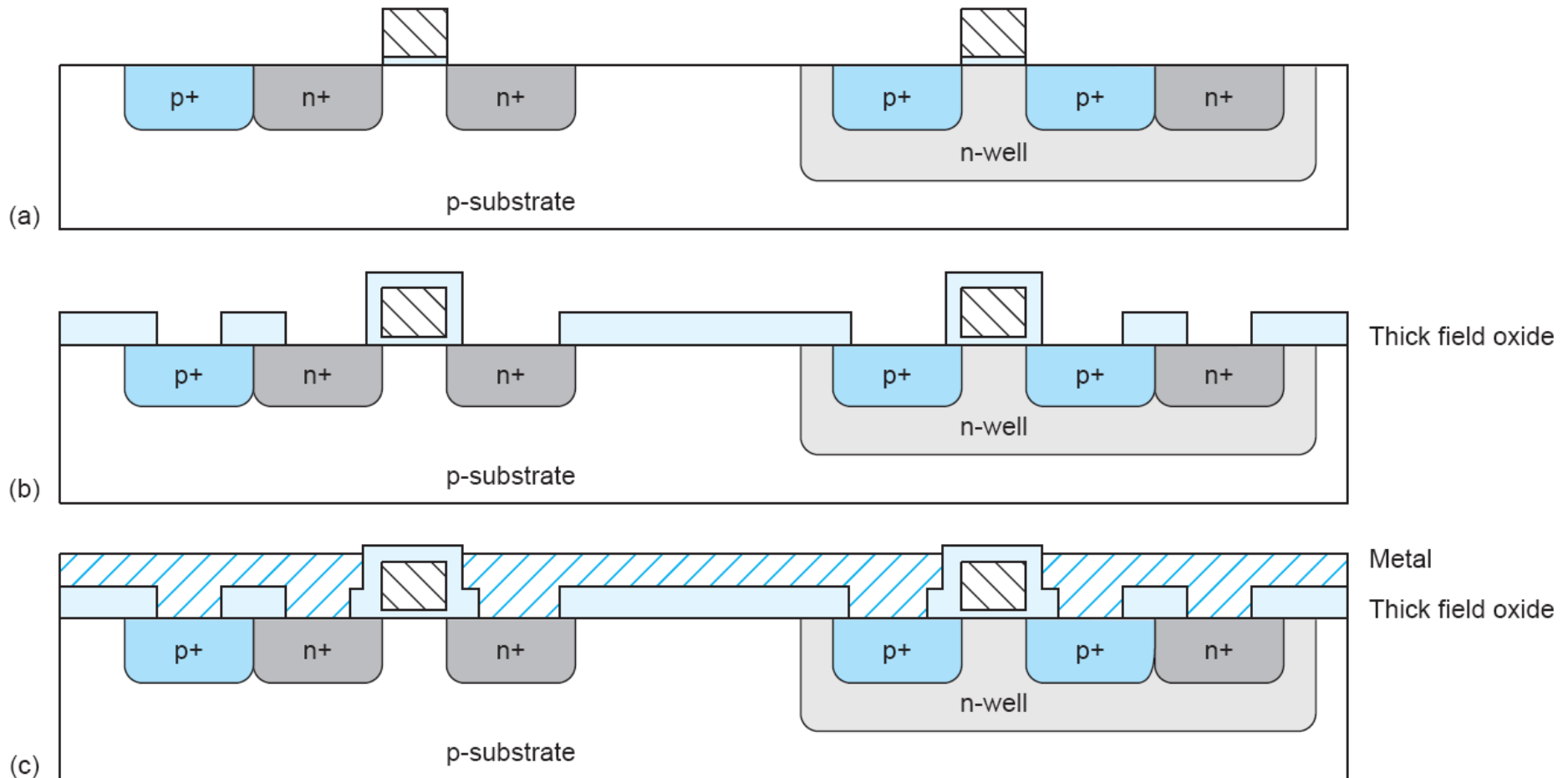


FIGURE 1.38 Cross-sections while manufacturing p-diffusion, contacts, and metal



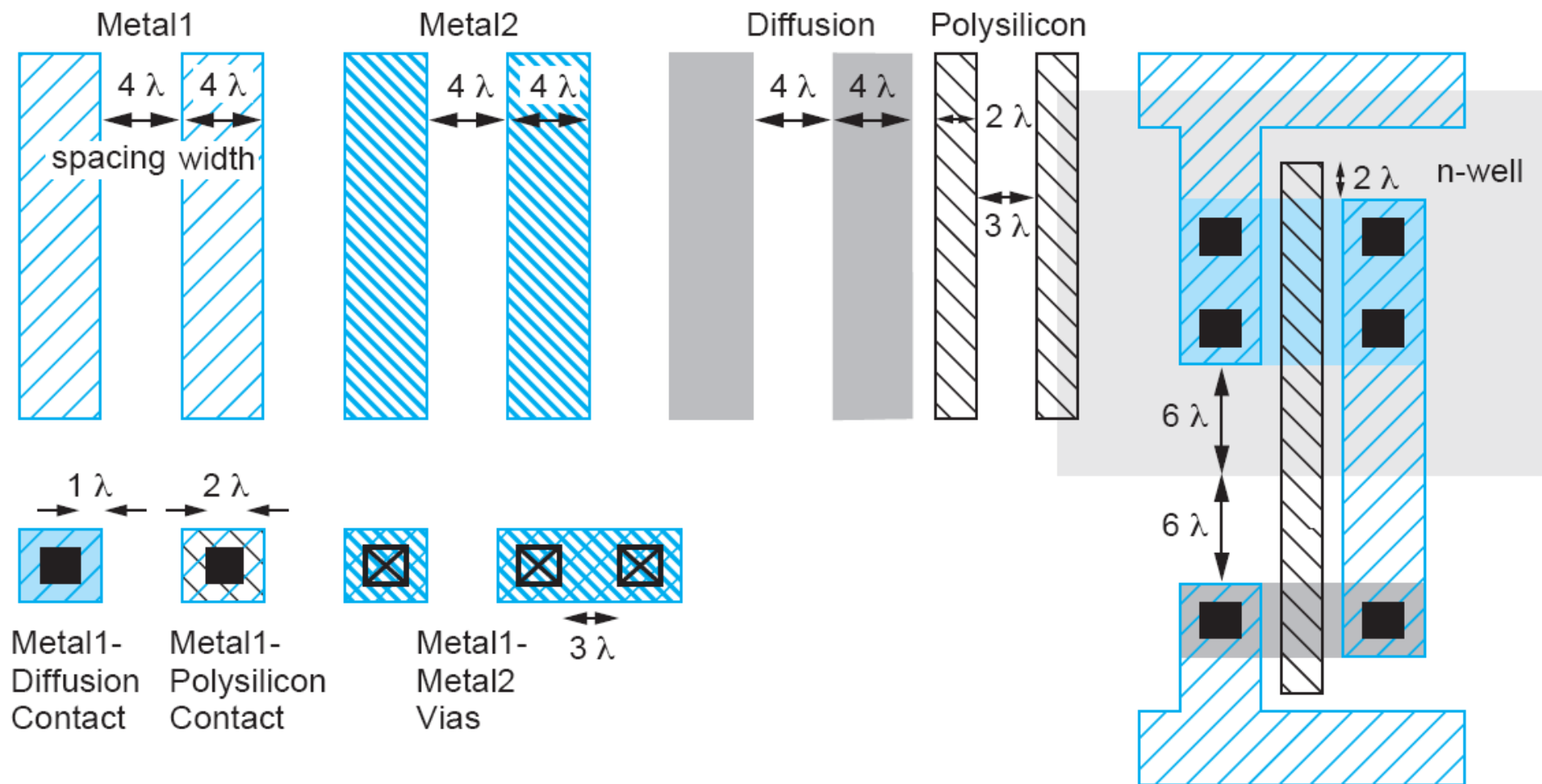


FIGURE 1.39 Simplified λ -based design rules



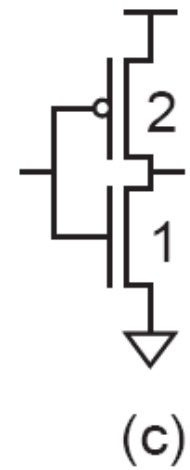
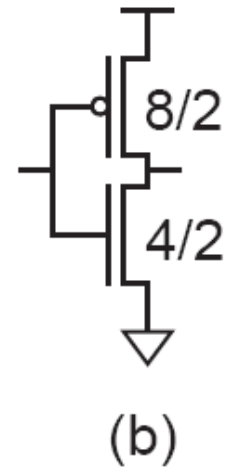
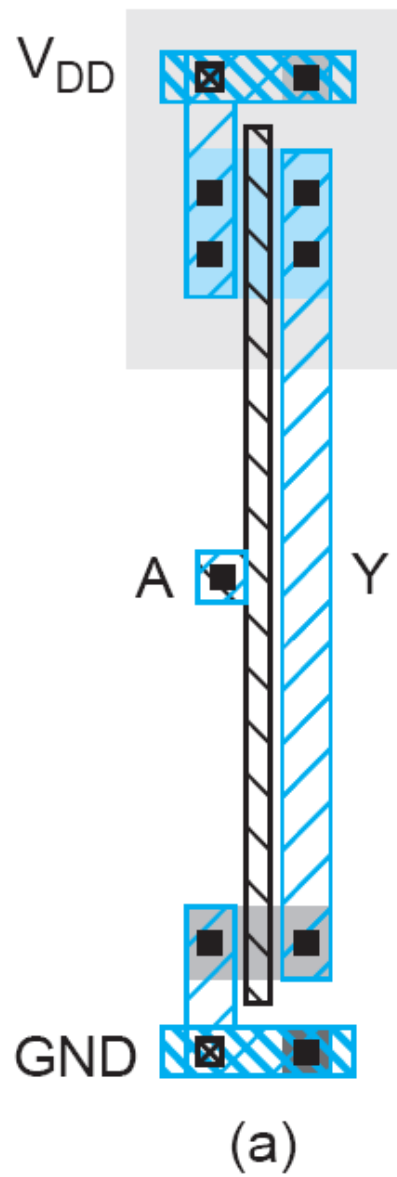


FIGURE 1.40 Inverter with dimensions labeled



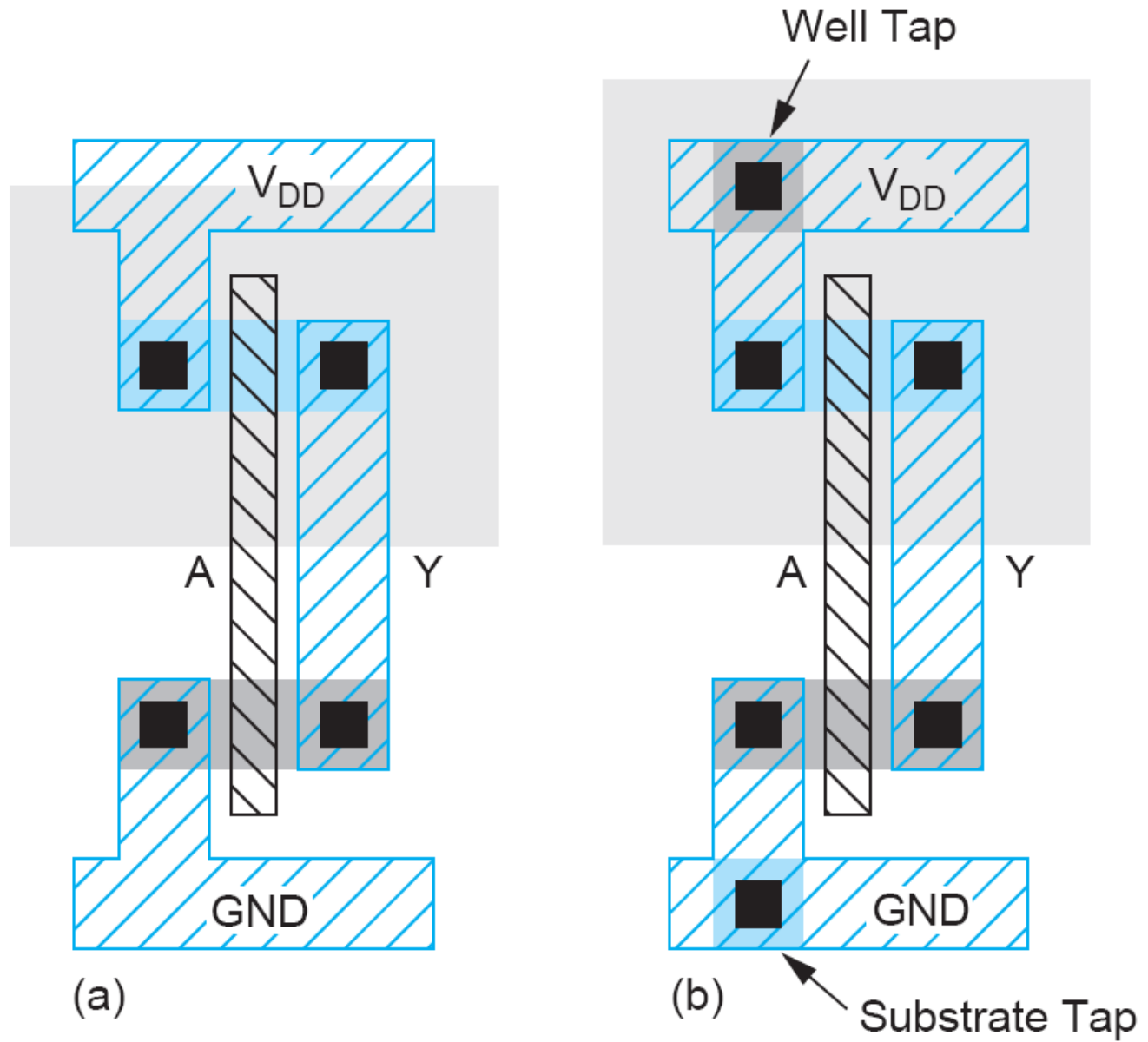


FIGURE 1.41 Inverter cell layout



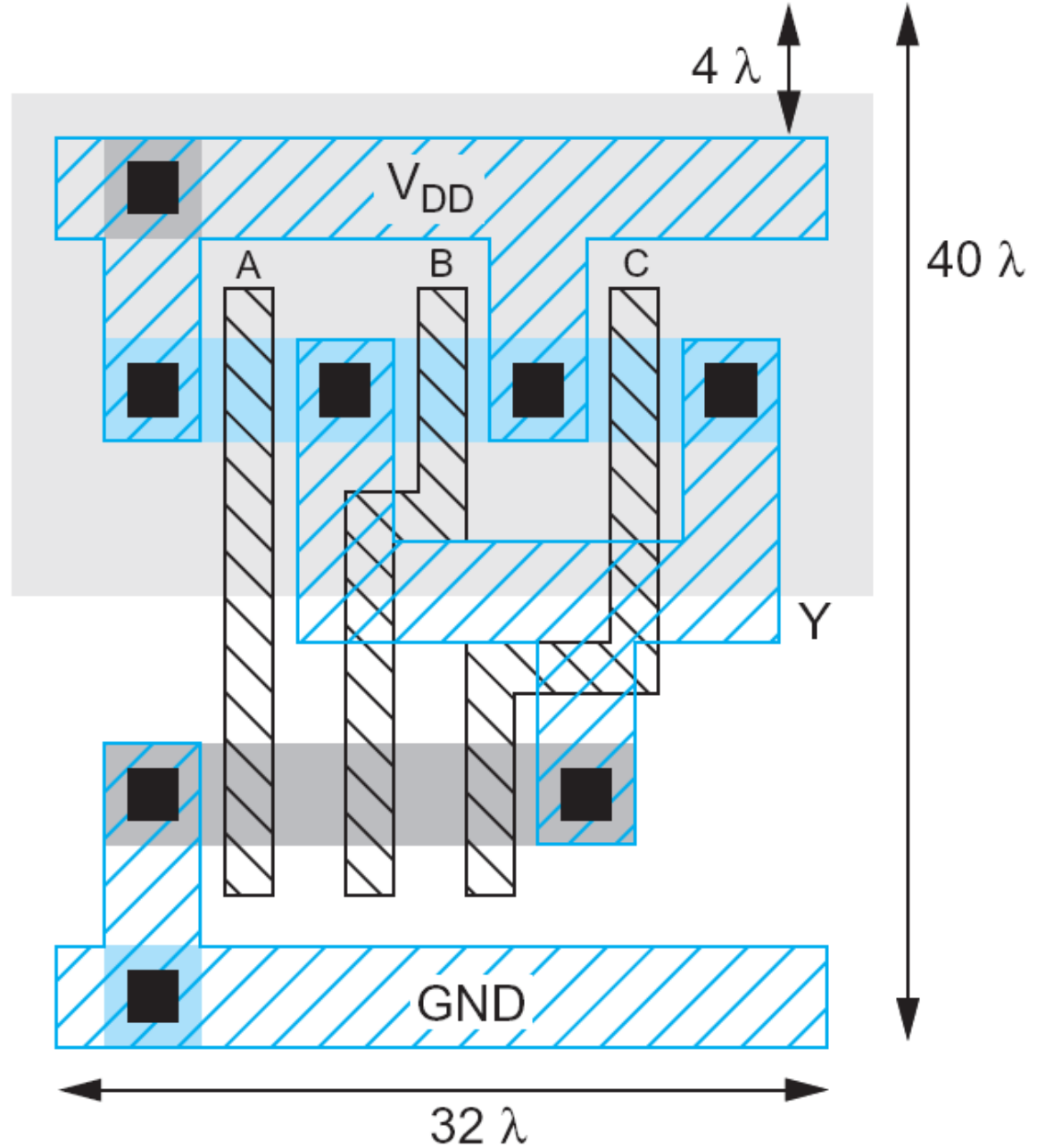


FIGURE 1.42 3-input NAND standard cell gate layouts



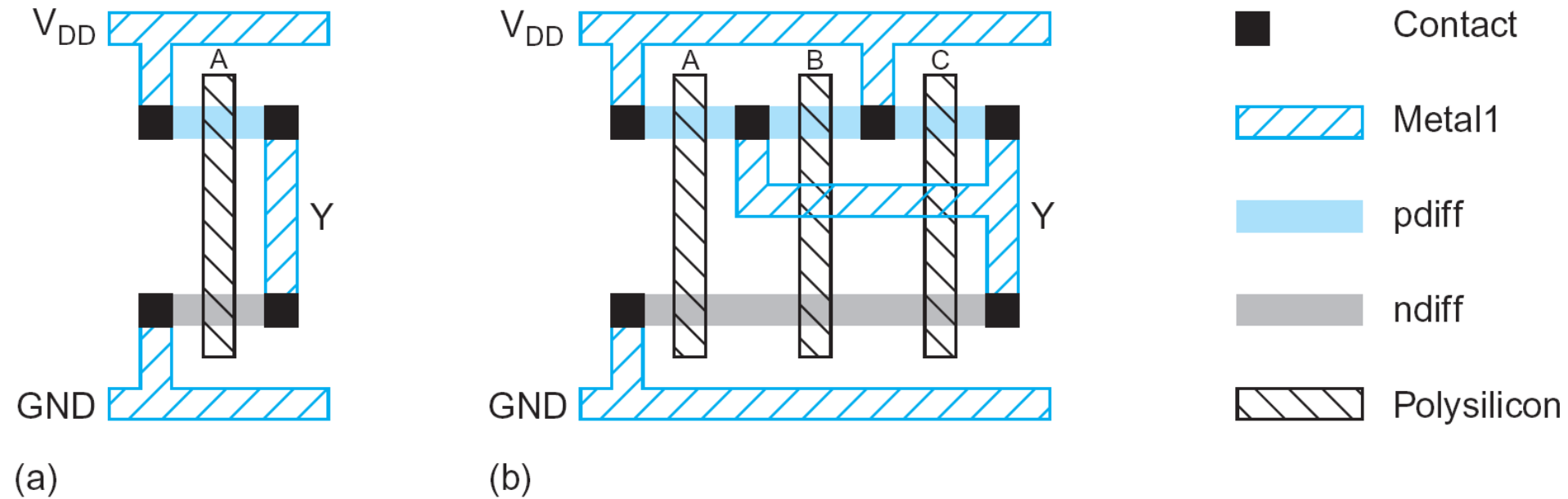
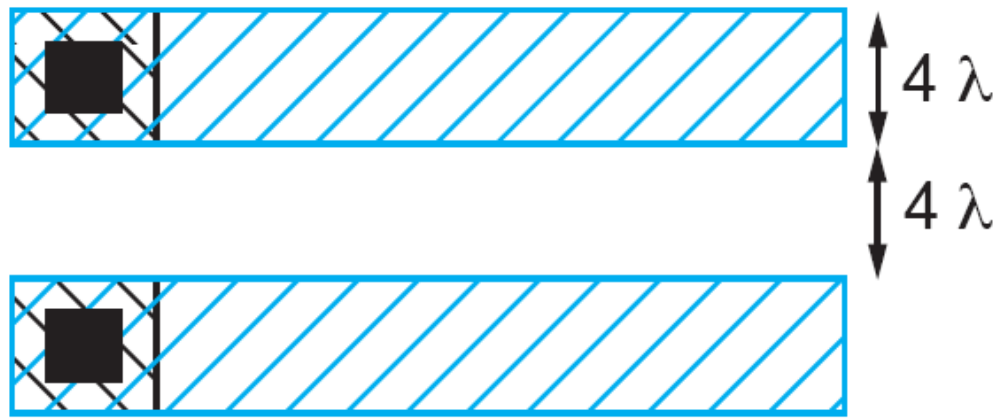
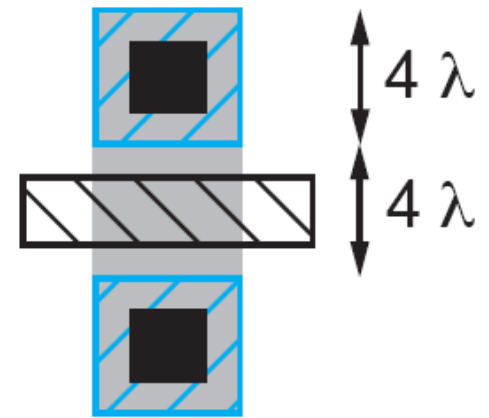


FIGURE 1.43 Stick diagrams of inverter and 3-input NAND gate. Color version on inside front cover.





(a)

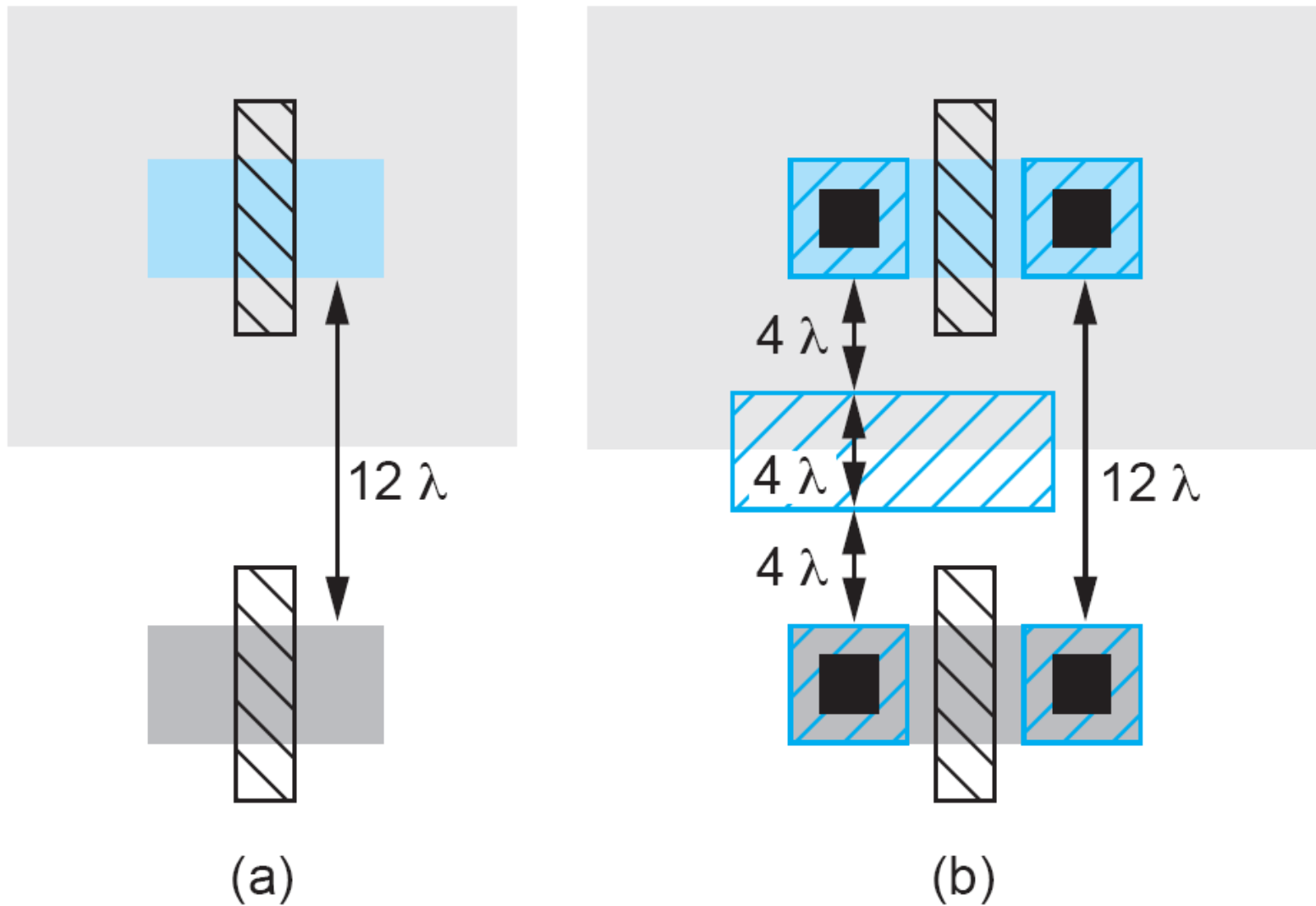


(b)

FIGURE 1.44 Pitch of routing tracks



FIGURE 1.45 Spacing between nMOS and pMOS transistors



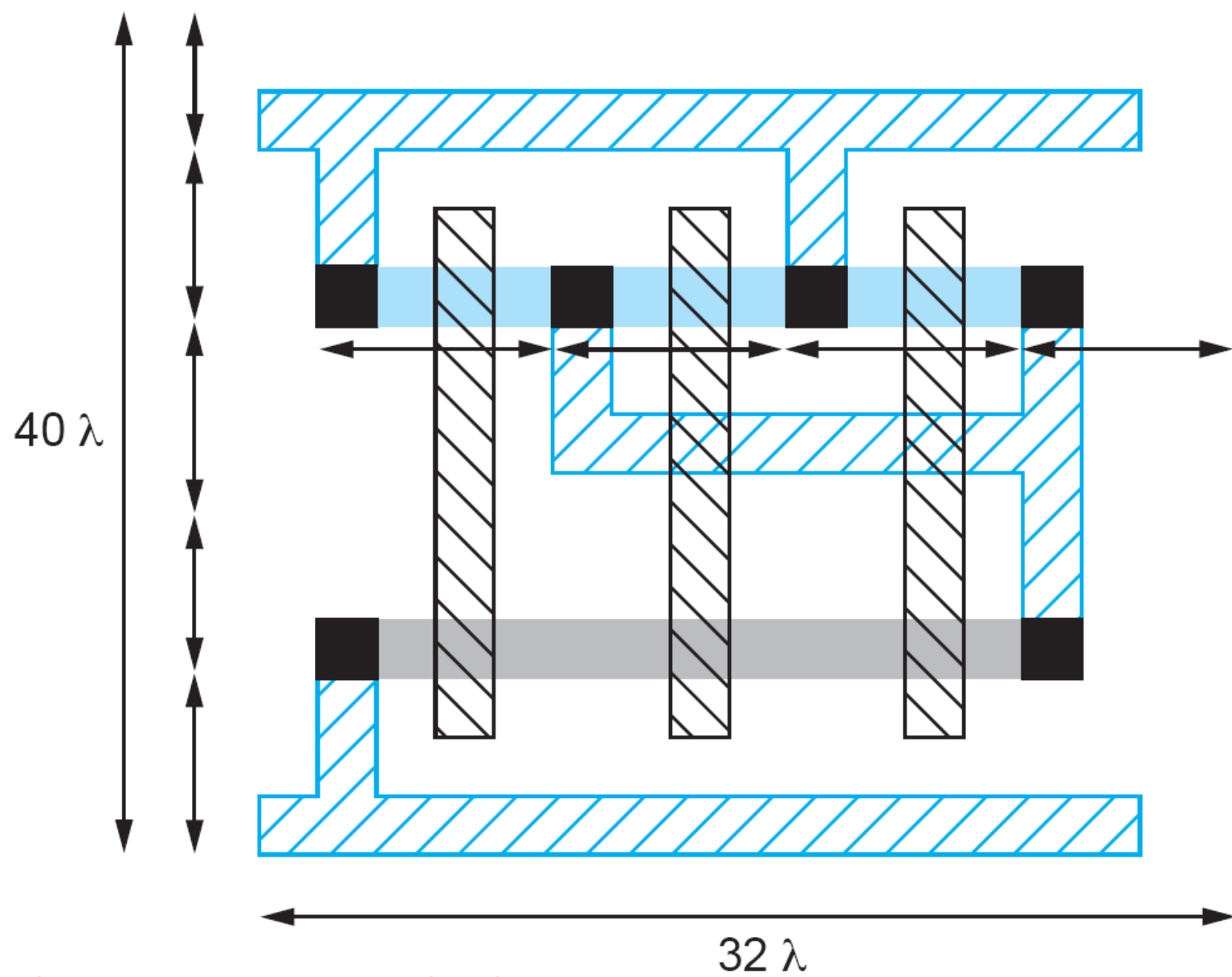


FIGURE 1.46 3-input NAND gate area estimation



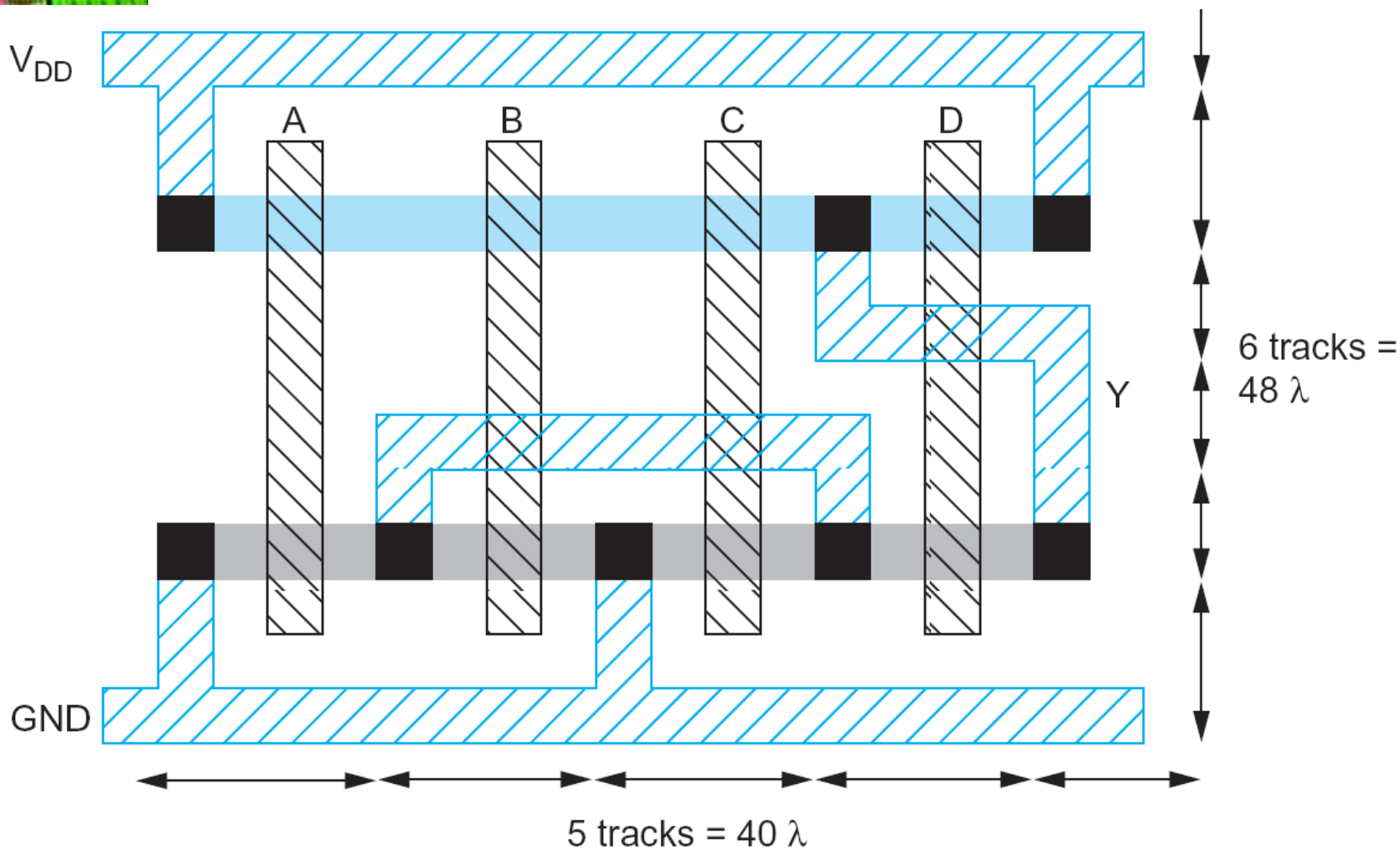


FIGURE 1.47 CMOS compound gate for function $Y = (A + B + C) \cdot D$

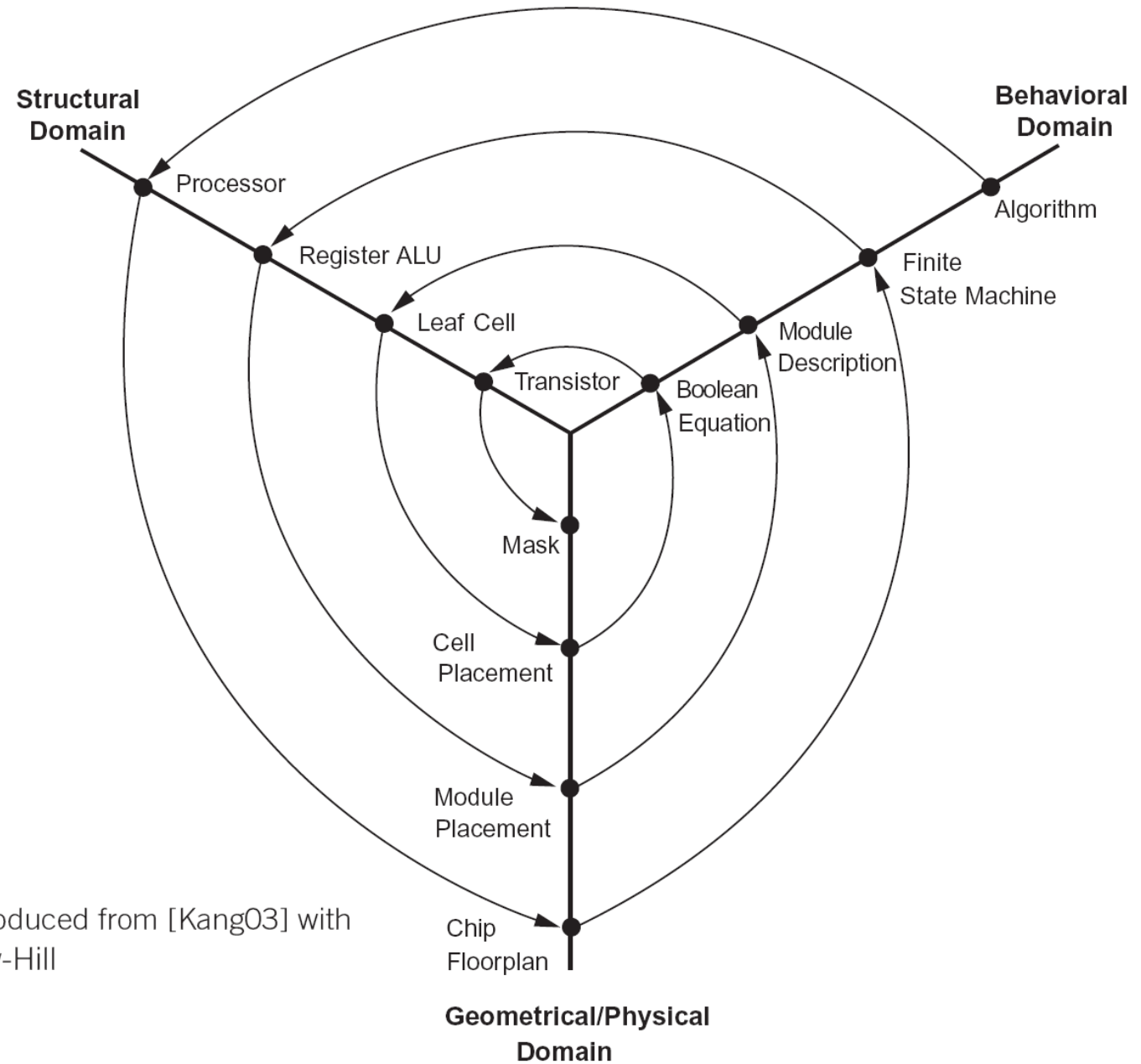


FIGURE 1.48 Y Diagram. Reproduced from [Kang03] with permission of The McGraw-Hill Companies.



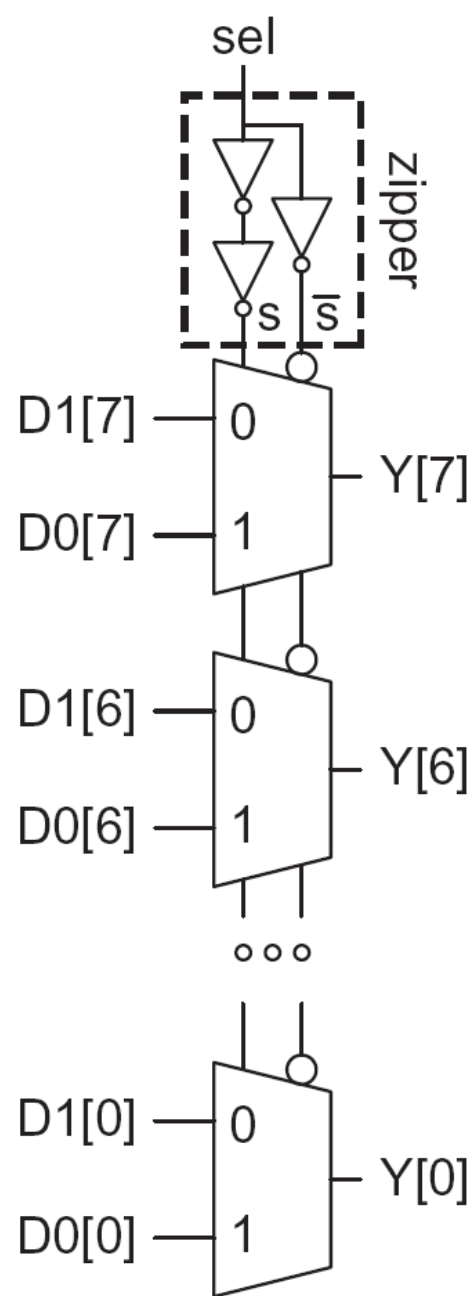


FIGURE 1.57 8-bit 2:1
multiplexer wordslice

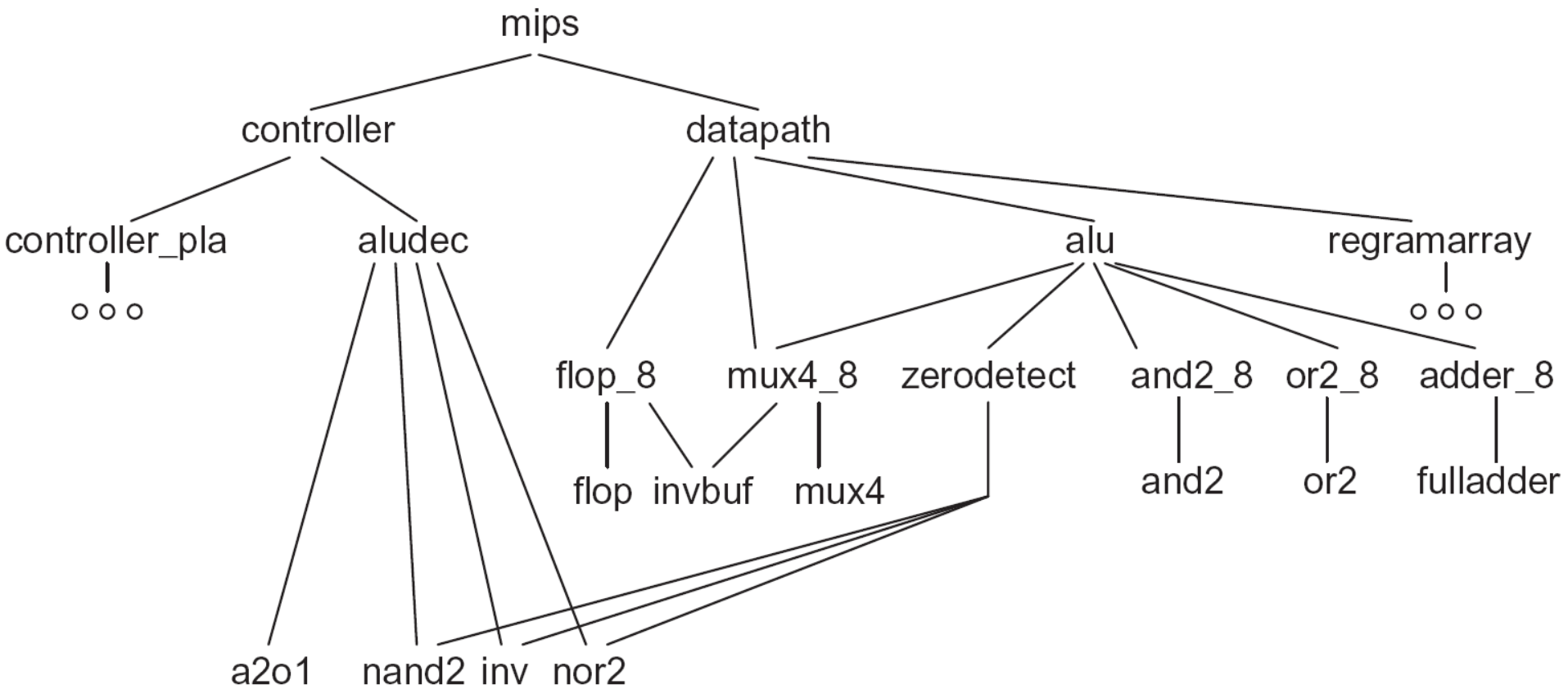


FIGURE 1.58 MIPS design hierarchy



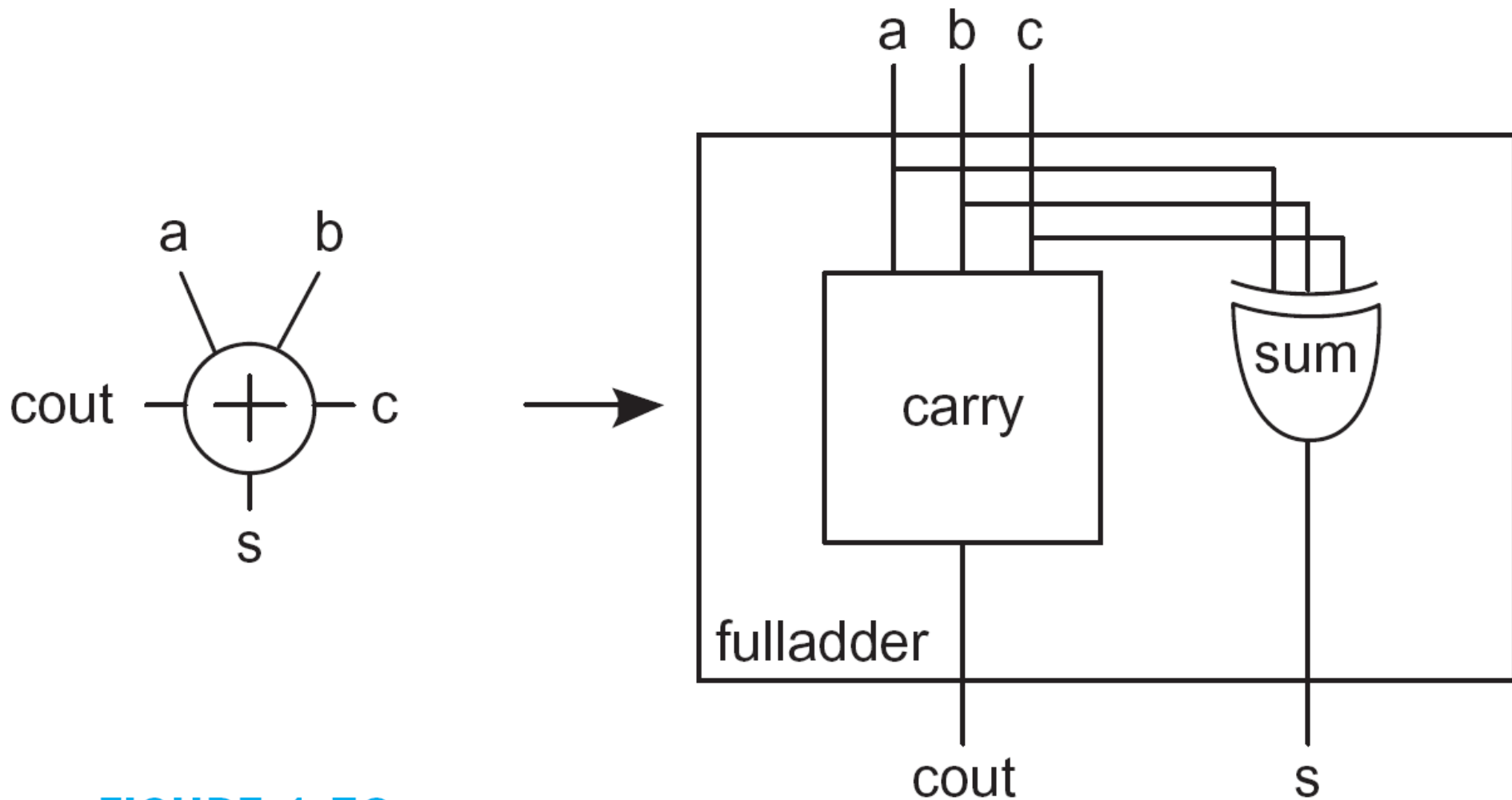
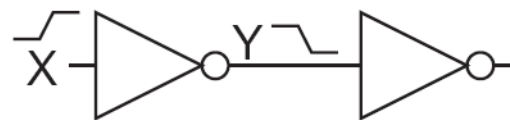
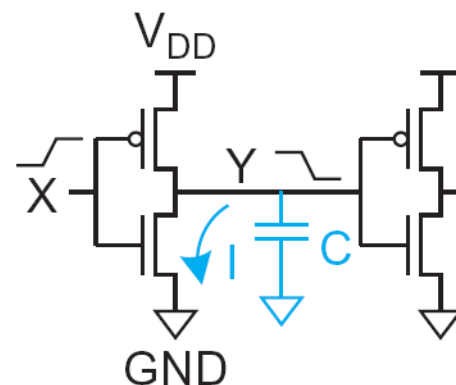


FIGURE 1.59 Full adder

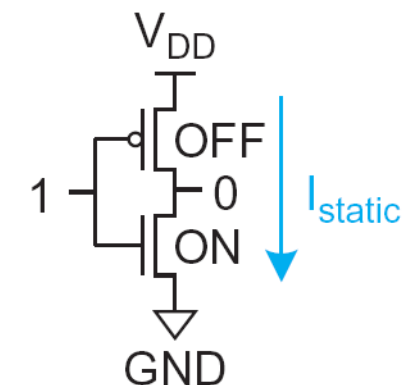




(a)



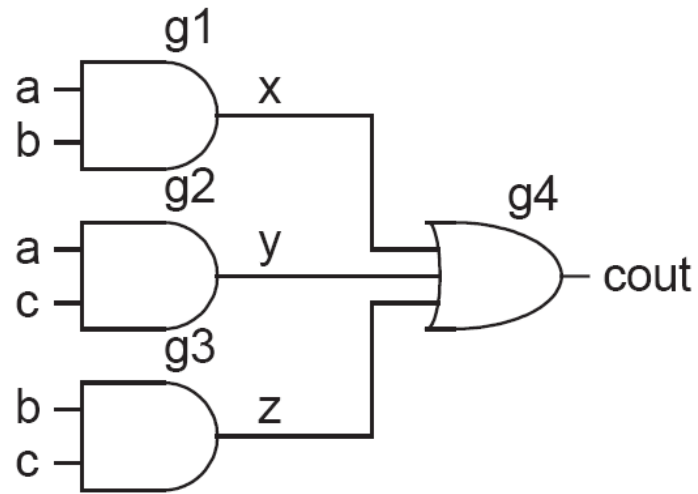
(b)



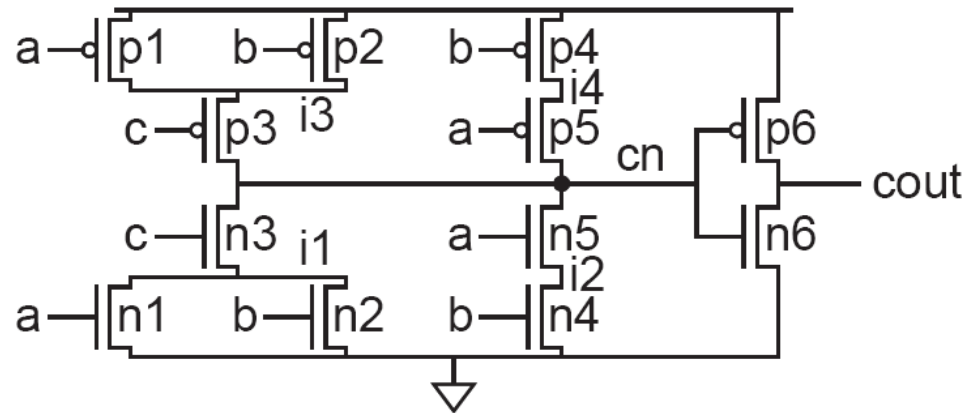
(c)

FIGURE 1.60 Circuit delay and power: (a) inverter pair, (b) transistor-level model showing capacitance and current during switching, (c) static leakage current during quiescent operation





(a)



(b)

FIGURE 1.61 Carry subcircuit



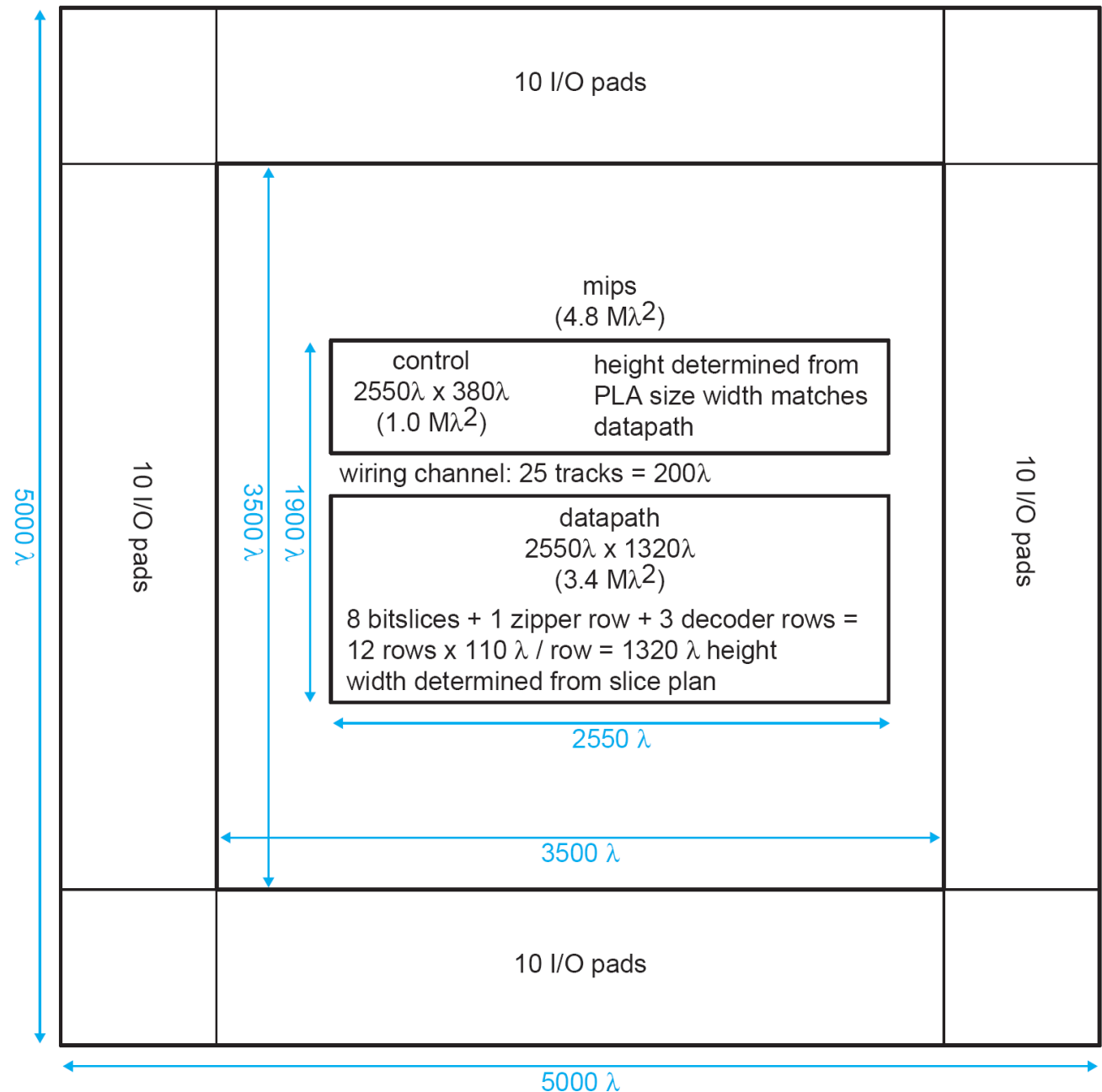


FIGURE 1.62 MIPS floorplan



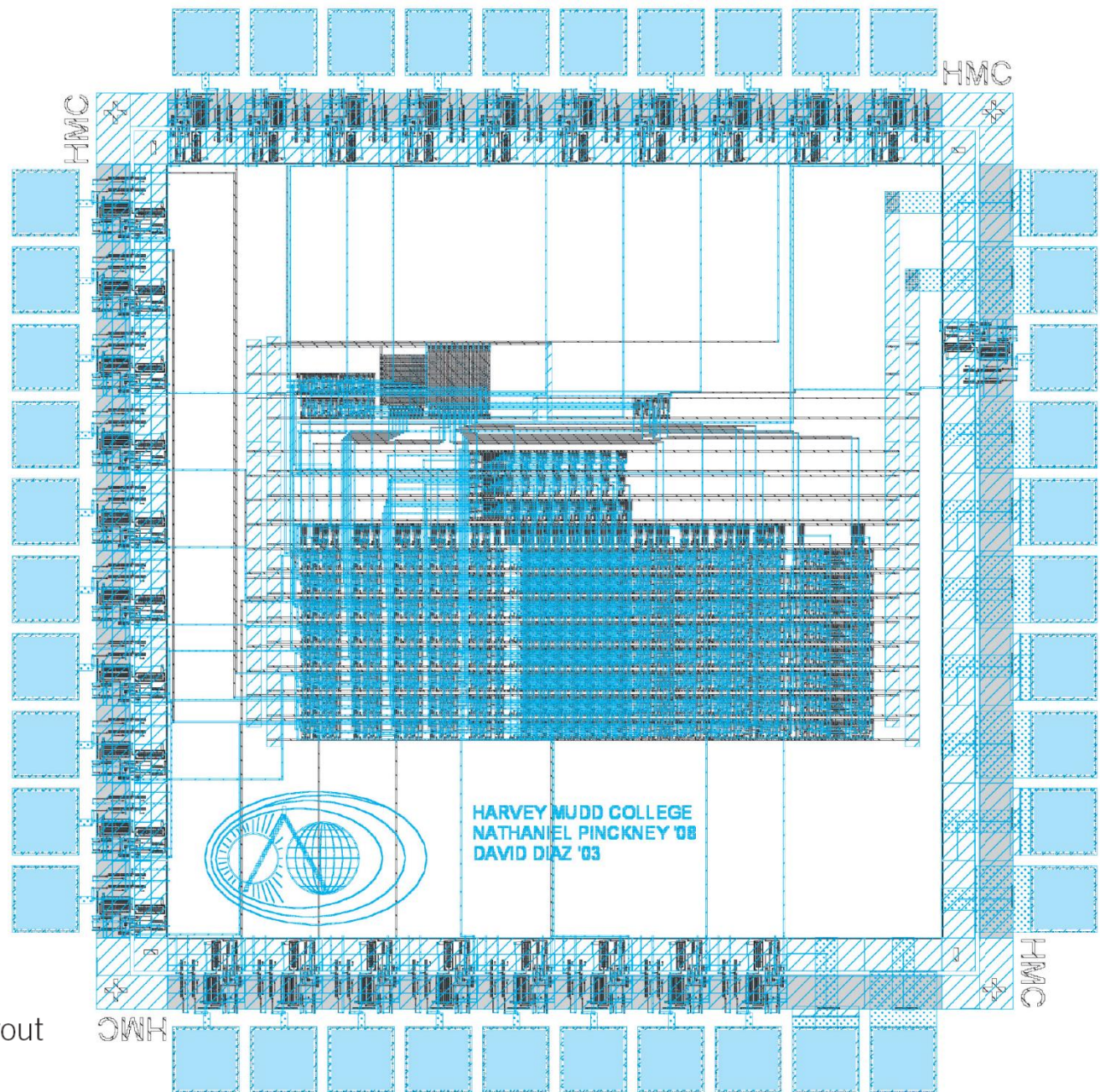


FIGURE 1.63 MIPS layout

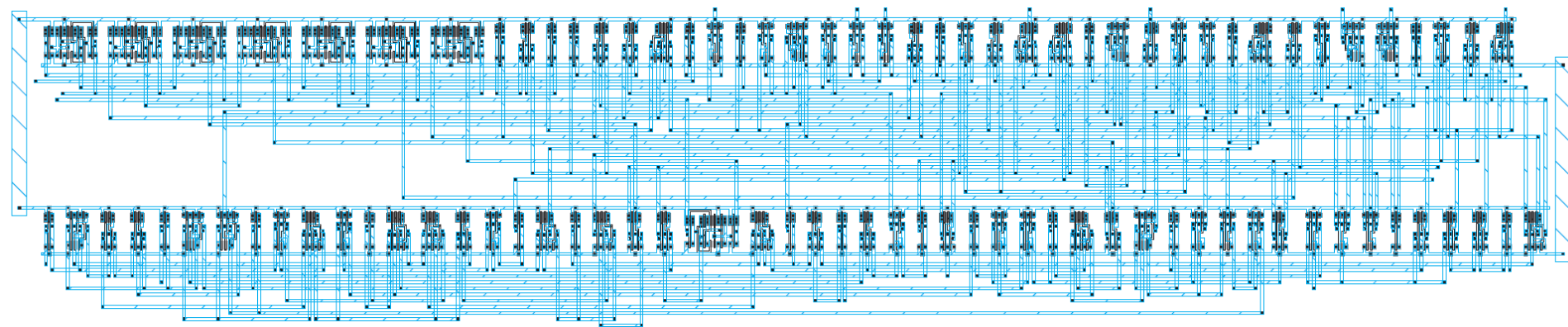


FIGURE 1.64 MIPS controller layout (synthesized)



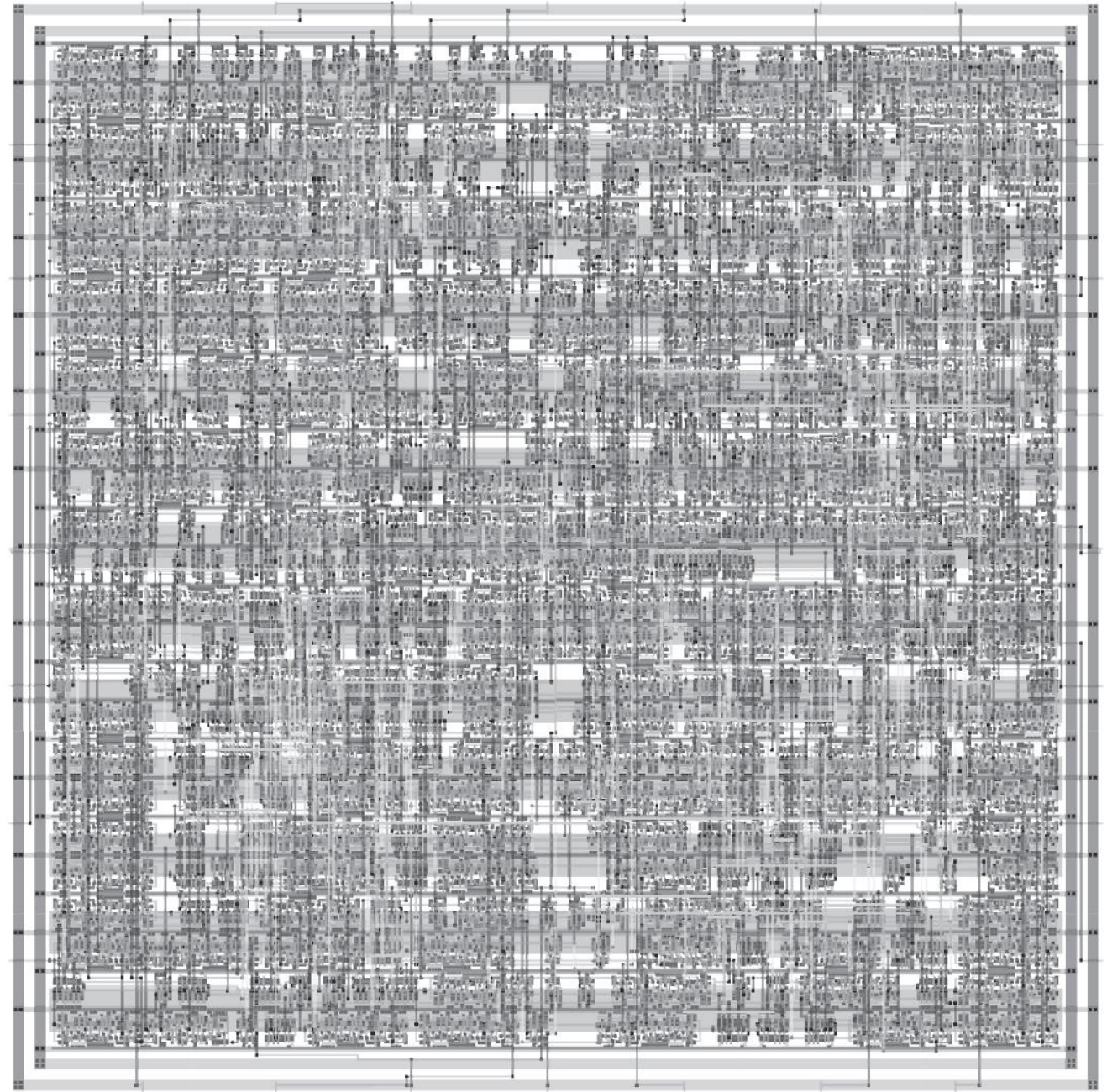


FIGURE 1.65 Synthesized MIPS processor





vdd gnd

Register File Decoder

vdd gnd

Zipper

Bitslice 7

Bitslice 0

flop
wordslice

mux
wordslice

adder
wordslice

FIGURE 1.67 MIPS datapath layout



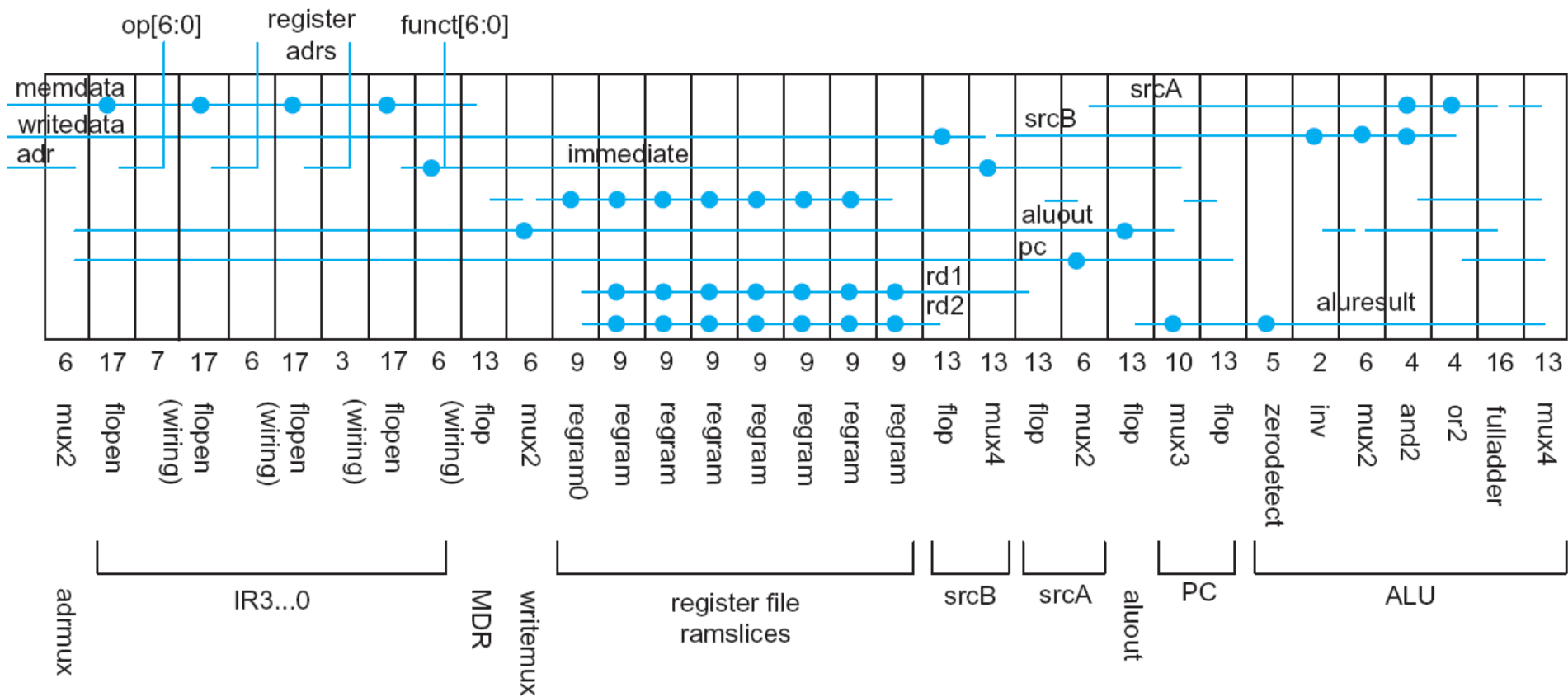


FIGURE 1.68 Datapath slice plan



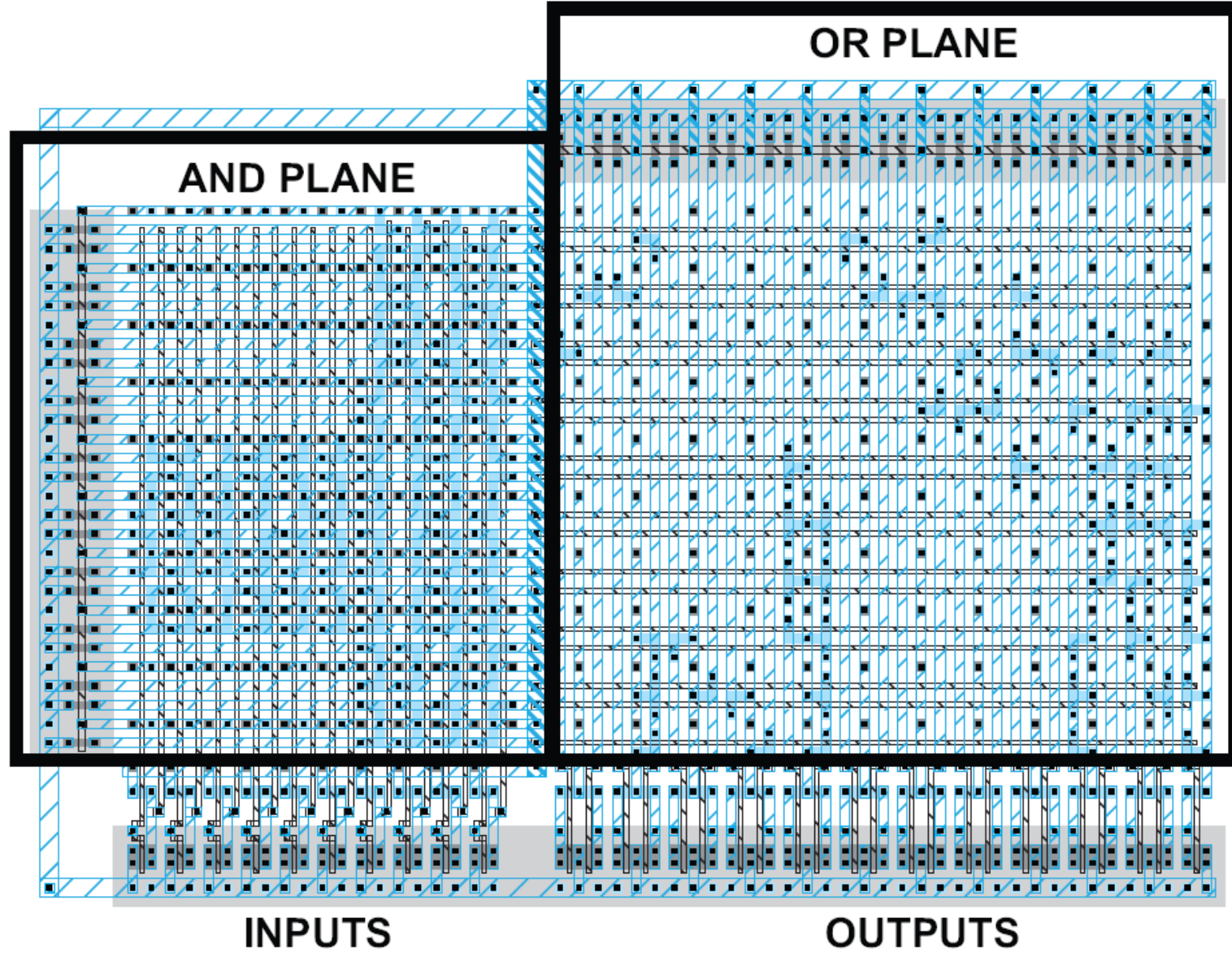


FIGURE 1.69 PLA for control FSM



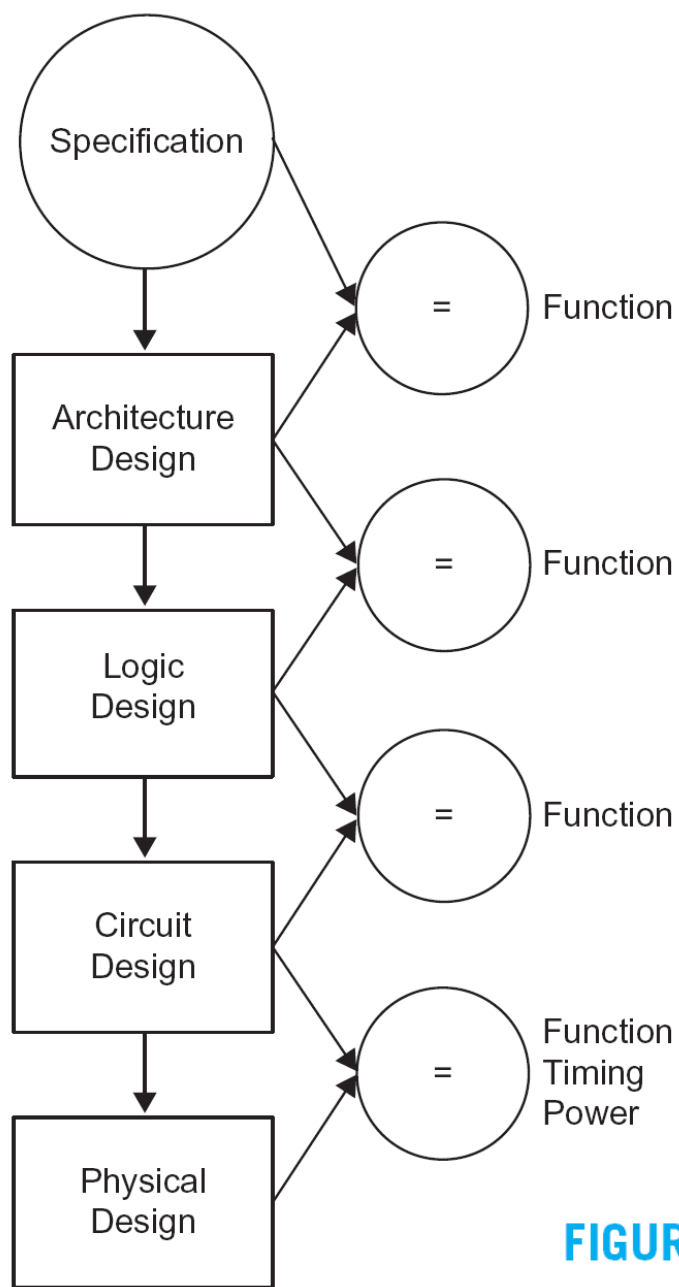


FIGURE 1.70 Design and verification sequence



FIGURE 1.71 Engineer holding processed 12-inch wafer. Photograph courtesy of the Intel Corporation.



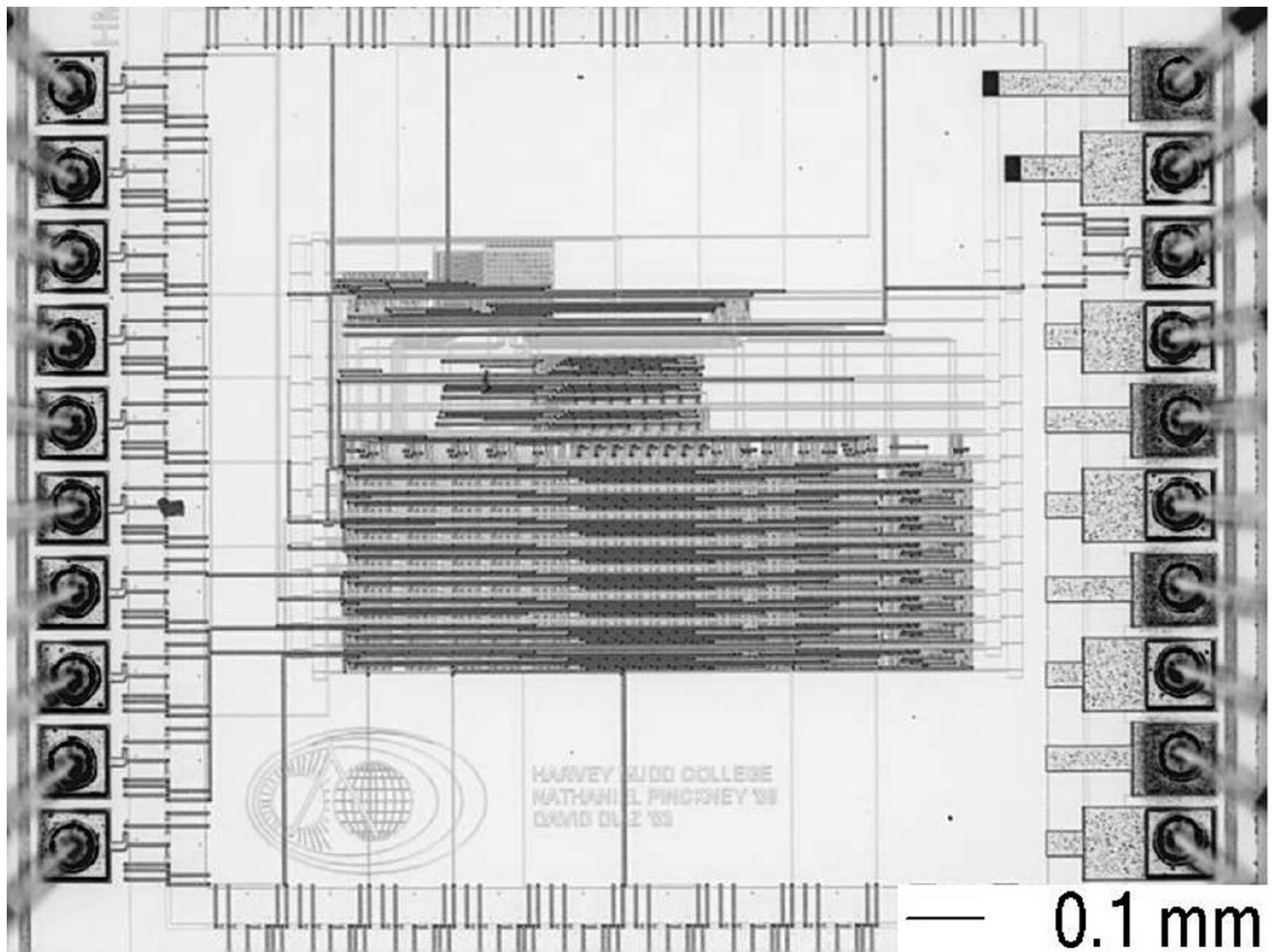


FIGURE 1.72 MIPS processor photomicrograph (only part of pad frame shown)

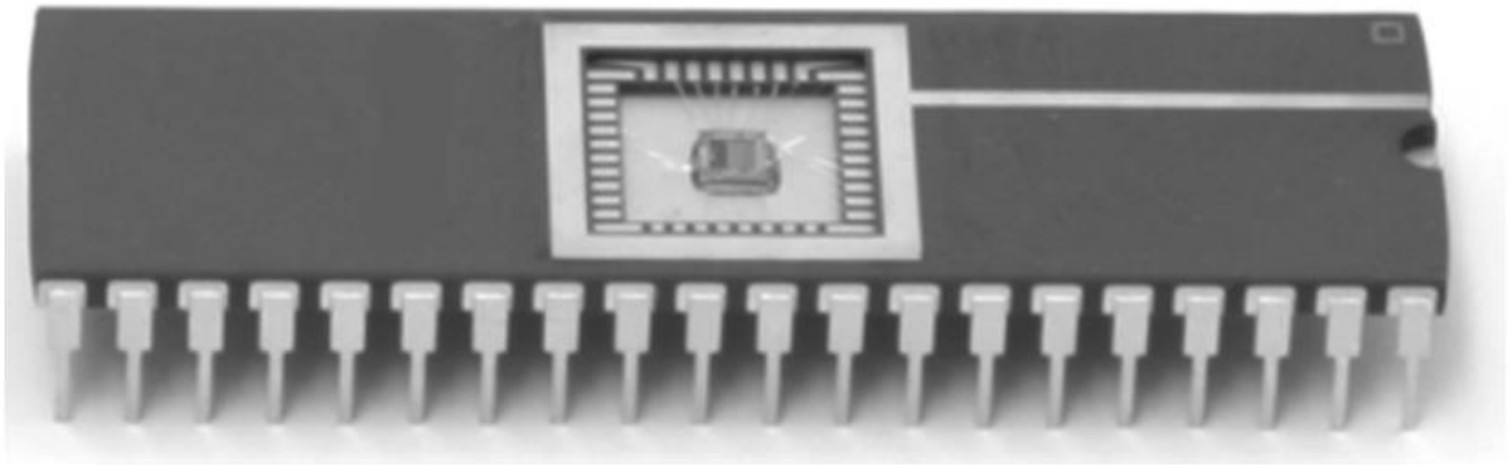


FIGURE 1.73 Chip in a 40-pin dual-inline package

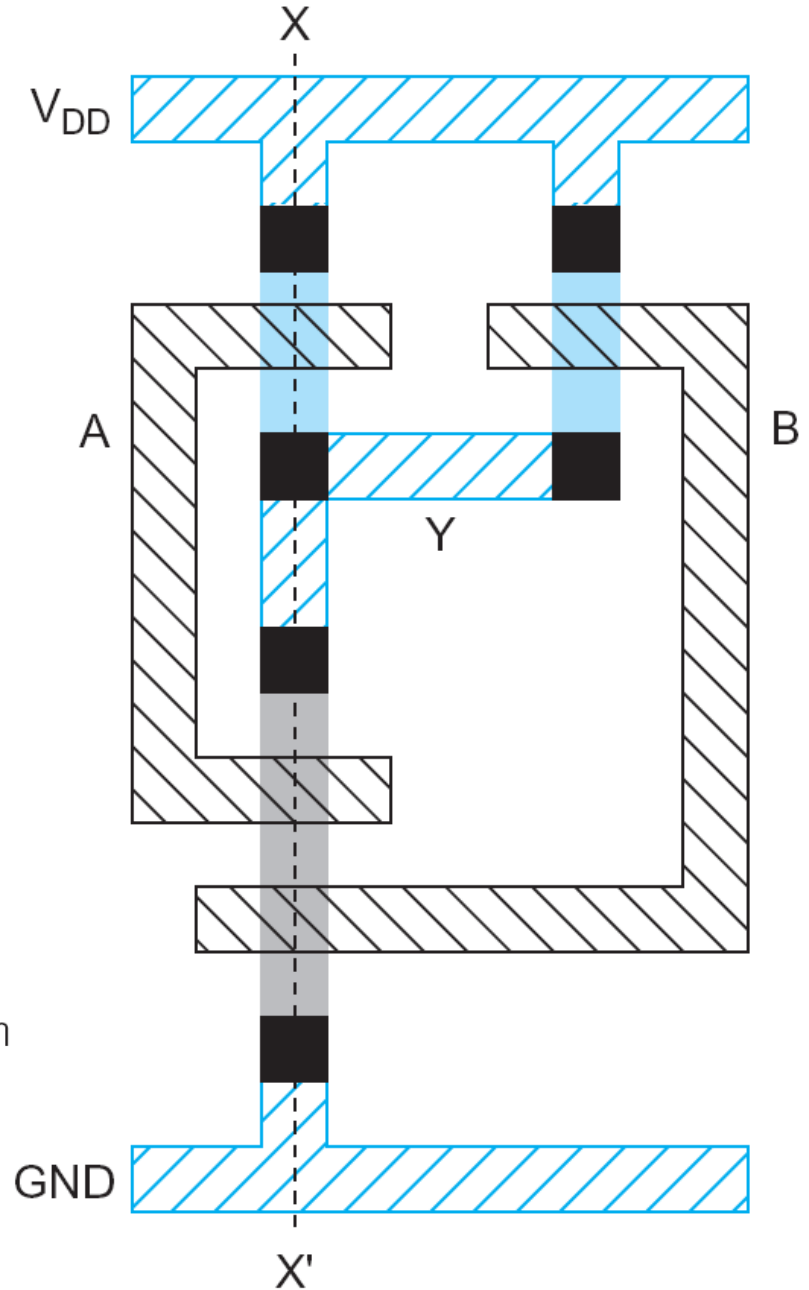


FIGURE 1.74 2-input NAND gate stick diagram



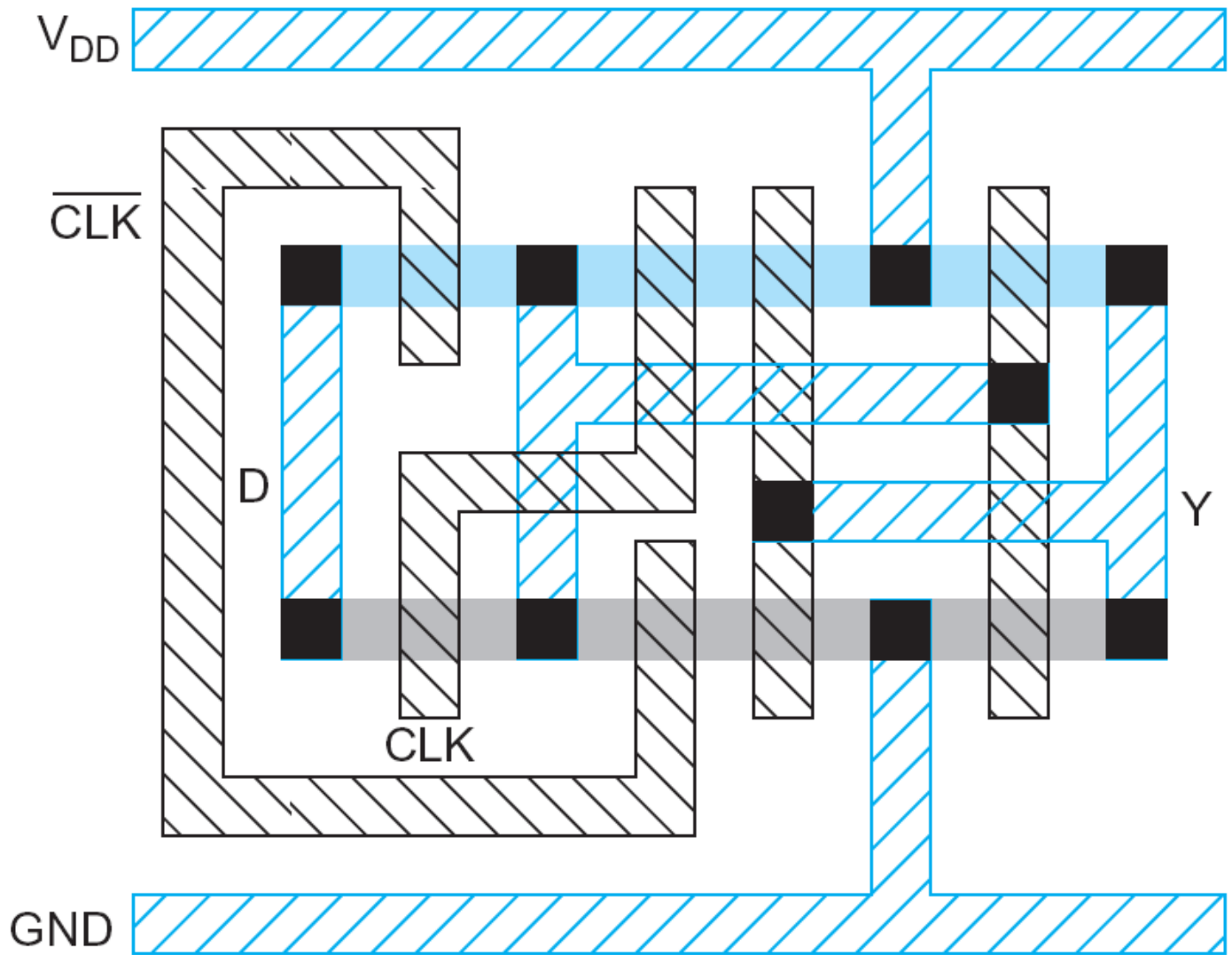


FIGURE 1.75 Level-sensitive latch stick diagram